

# EE 330

## Lecture 8

Stick Diagrams

Technology Files

- Design Rules
- Process Flow
- Model Parameters

Photo courtesy of the director of the National Institute of Health ( NIH)



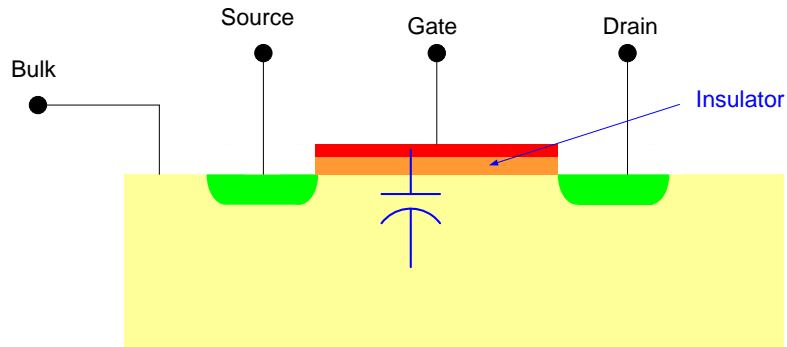
As a courtesy to fellow classmates, TAs, and the instructor

**Wearing of masks during lectures and in the laboratories for this course would be appreciated irrespective of vaccination status**

## Review from Last Time

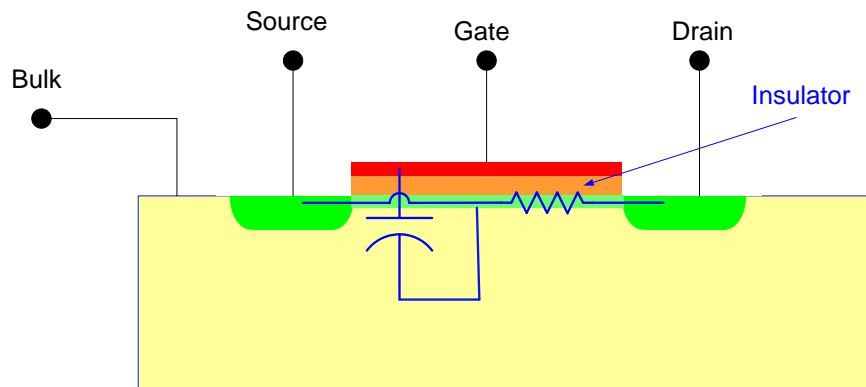
# MOS Transistor

## Qualitative Discussion of n-channel Operation



n-channel MOSFET

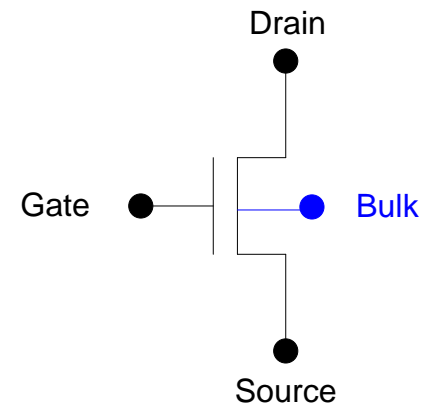
For  $V_{GS}$  small



n-channel MOSFET

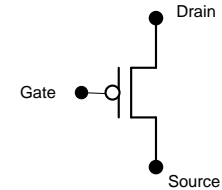
For  $V_{GS}$  large

- Electrically created inversion layer forms a “thin “film” resistor
- Capacitance from gate to channel region is distributed
- Lumped capacitance much easier to work with

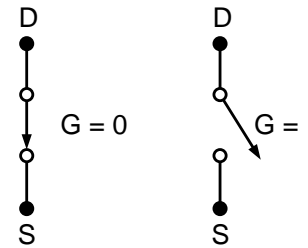


## Review from Last Time

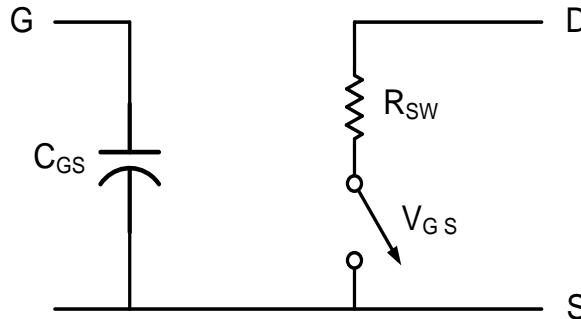
# Model Summary (for p-channel)



### 1. Switch-Level model



### 2. Improved switch-level model

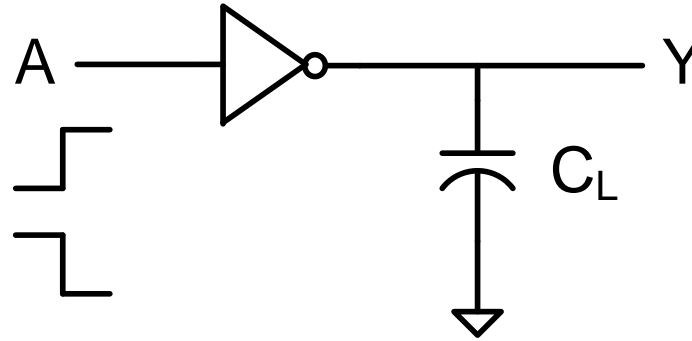


*Switch closed for  $|V_{GS}| = \text{large}$   
Switch open for  $|V_{GS}| = \text{small}$*

*Other models will be developed later*

## Review from Last Time

### Response time of logic gates



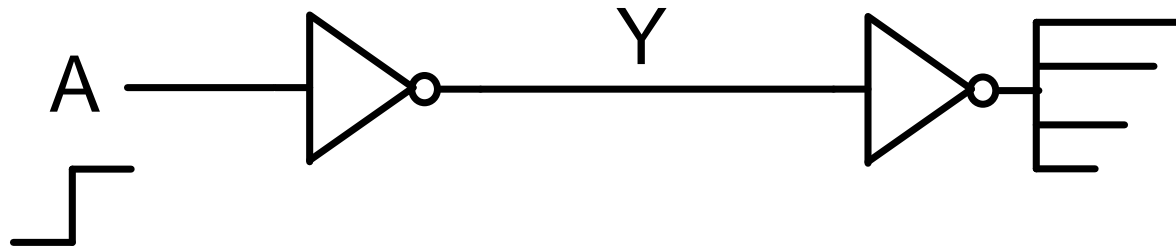
$$t_{HL} \cong R_{SWn} C_L$$

$$t_{LH} \cong R_{SWp} C_L$$

- Logic Circuits can operate very fast
- Extremely small parasitic capacitances play key role in speed of a circuit

## Review from Last Time

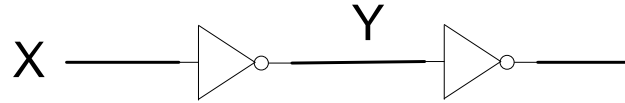
*One gate often drives one or more other gates !*



*What are  $t_{HL}$  and  $t_{LH}$ ?*

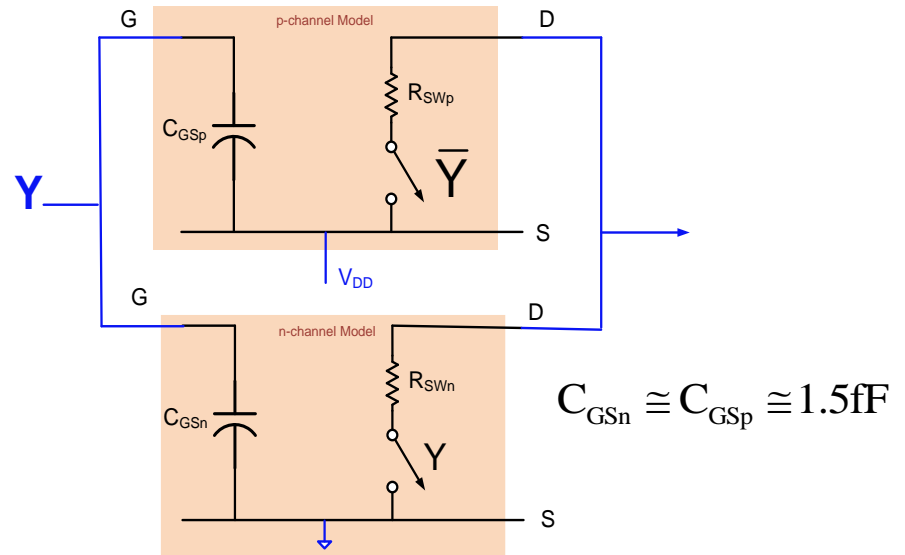
# Review from Last Time

Example: What is the delay of a minimum-sized inverter driving another identical device?

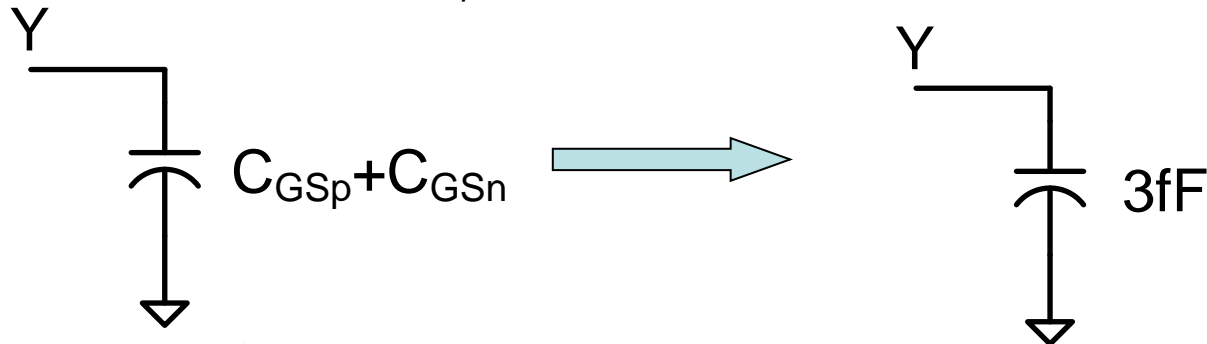


Load on first inverter

$C_{GSn}$  and  $C_{GSp}$  both 1.5fF



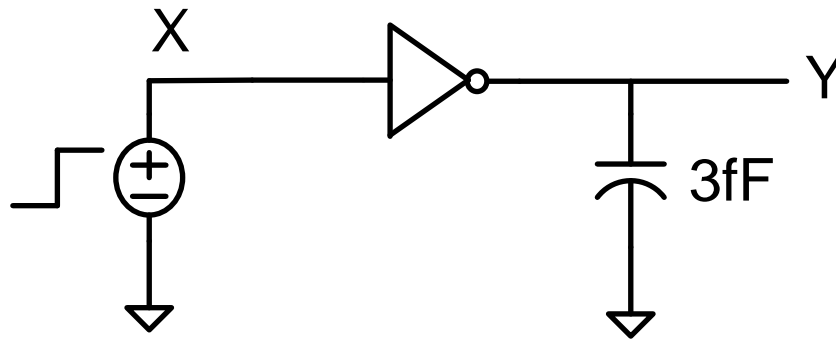
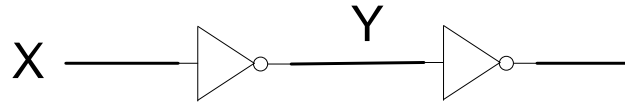
Loading effects same whether  $C_{GSp}$  and/or  $C_{GSn}$  connected to  $V_{DD}$  or GND



For convenience, will reference both to ground

## Review from Last Time

Example: What is the delay of a minimum-sized inverter driving another identical device?



$$t_{HL} \cong R_{SWn} C_L = 2K \bullet 3fF = 6p \text{ sec}$$

$$t_{LH} \cong R_{SWp} C_L = 6K \bullet 3fF = 18p \text{ sec}$$

Do gates really operate this fast?

What would be the maximum clock rate for acceptable operation?



## Review from Last Time

# Some Observations about Technology and Politics

US Government has recognized that investment in the semiconductor industry is critical to regain technical dominance in the field

The US is now in a serious catchup position because except for Intel, US technology is now about a decade behind foreign competitors

**A recent announcement looks promising for the future !**

<https://www.washingtonpost.com> › 2021/06/14 › global... ⋮

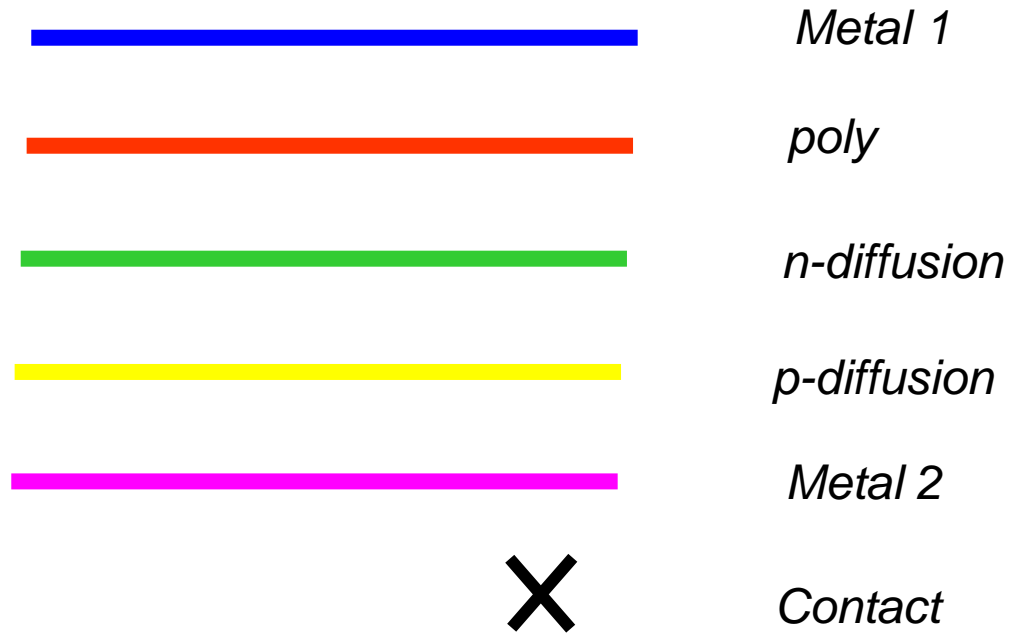
**Senate approved \$52 billion in subsidies for chip manufacturing**

Will this investment close the gap that exists today in semiconductor technology or actually reverse the world order in the semiconductor industry?

# Stick Diagrams

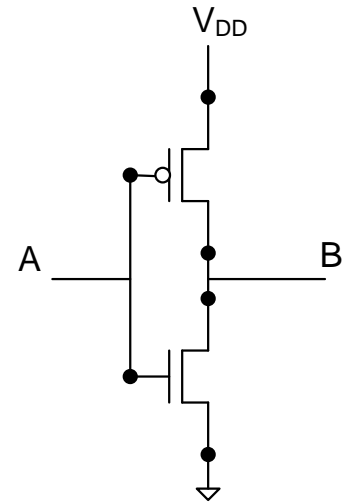
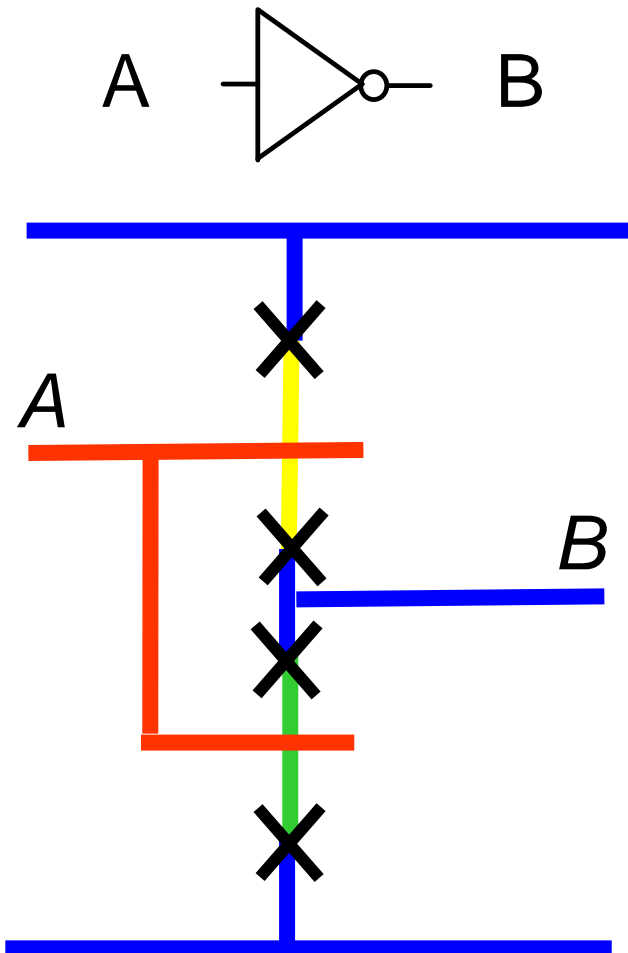
- It is often necessary to obtain information about placement, interconnect and physical-layer structure
- Stick diagrams are often used for small component-count blocks
- Approximate placement, routing, and area information can be obtained rather quickly with the use of stick diagrams

# Stick Diagrams



*Additional layers can be added and color conventions are personal*

# Stick Diagram

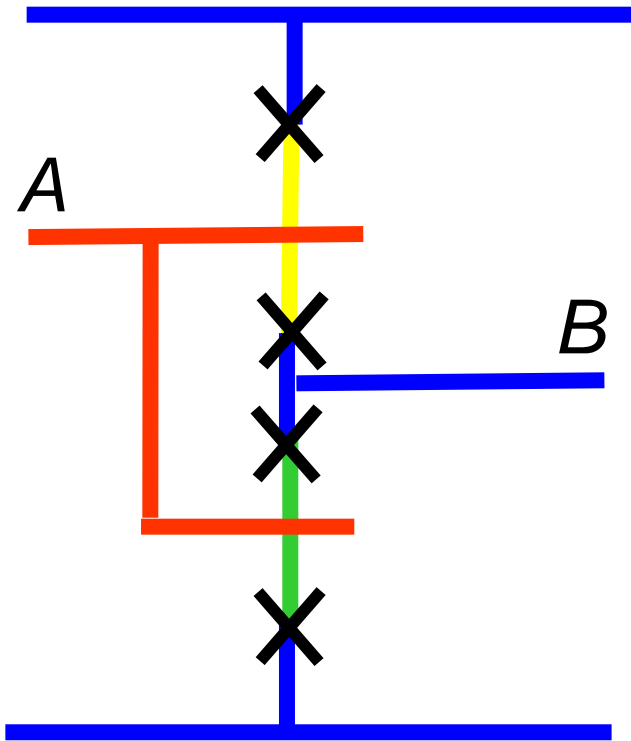
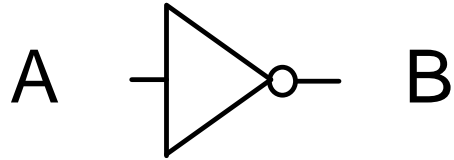


*A stick diagram is not a layout but gives the basic structure (including location,, orientation and interconnects) that will be instantiated in the actual layout itself*

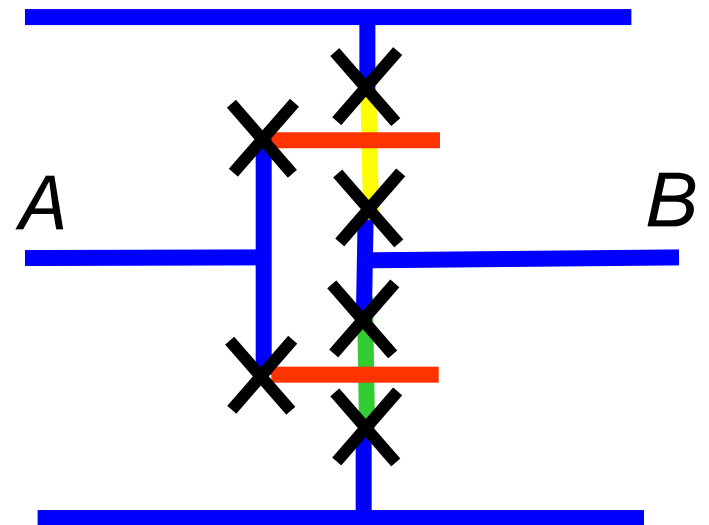
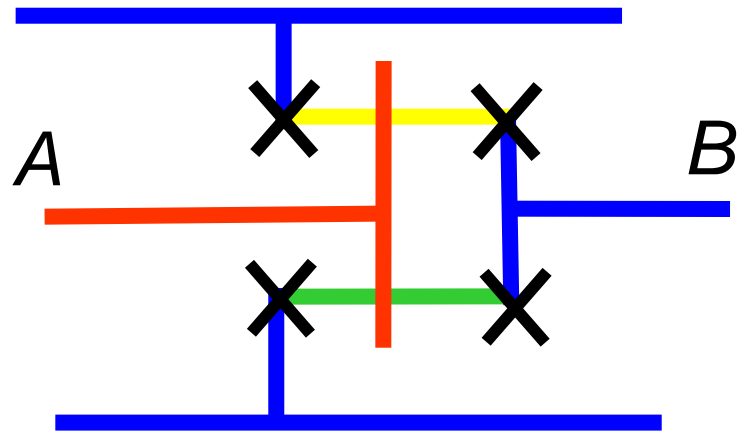
*Modifications can be made much more quickly on a stick diagram than on a layout*

*Iteration may be needed to come up with a good layout structure*

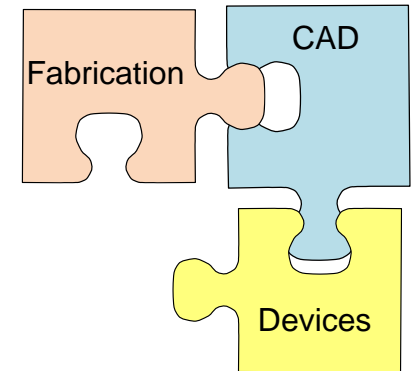
# Stick Diagram



*Alternate Representations*



# Technology Files



- Provide Information About Process
  - Process Flow (Fabrication Technology)
  - Model Parameters
  - Design Rules
- Serve as Interface Between Design Engineer and Process Engineer
- Insist on getting information that is deemed important for a design
  - Limited information available in academia
  - Foundries often sensitive to who gets access to information
  - Customer success and satisfaction is critical to foundries

# Technology Files

- Design Rules
- Process Flow (Fabrication Technology) (will discuss next )
- Model Parameters (will discuss in substantially more detail after device operation and more advanced models are introduced)

First – A preview of what the technology files look like !

## Typical Design Rules

**TABLE 2B.2**  
**Design rules for a typical p-well CMOS process**  
 (See Table 2B.3 in color plates for graphical interpretation)

	Dimensions	
	Microns	Scalable
1. p-well (CIF Brown, Mask #1 <sup>a</sup> )		
1.1 Width	5	4 $\lambda$
1.2 Spacing (different potential)	15	10 $\lambda$
1.3 Spacing (same potential)	9	6 $\lambda$
2. Active (CIF Green, Mask #2)		
2.1 Width	4	2 $\lambda$
2.2 Spacing	4	2 $\lambda$
2.3 p <sup>+</sup> active in n-sub to p-well edge	8	6 $\lambda$
2.4 n <sup>+</sup> active in n-sub to p-well edge	7	5 $\lambda$
2.5 n <sup>+</sup> active in p-well to p-well edge	4	2 $\lambda$
2.6 p <sup>+</sup> active in p-well to p-well edge	1	$\lambda$
3. Poly (POLY I) (CIF Red, Mask #3)		
3.1 Width	3	2 $\lambda$
3.2 Spacing	3	2 $\lambda$
3.3 Field poly to active	2	$\lambda$
3.4 Poly overlap of active	3	2 $\lambda$
3.5 Active overlap of poly	4	2 $\lambda$
4. p <sup>+</sup> select (CIF Orange, Mask #4)		
4.1 Overlap of active	2	$\lambda$
4.2 Space to n <sup>+</sup> active	2	$\lambda$
4.3 Overlap of channel <sup>b</sup>	3.5	2 $\lambda$
4.4 Space to channel <sup>b</sup>	3.5	2 $\lambda$
4.5 Space to p <sup>+</sup> select	3	2 $\lambda$
4.6 Width	3	2 $\lambda$



## Typical Design Rules (cont)

5.	Contact <sup>c</sup> (CIF Purple, Mask #6)		
5.1	Square contact, exactly	$3 \times 3$	$2\lambda \times 2\lambda$
5.2	Rectangular contact, exactly	$3 \times 8$	$2\lambda \times 6\lambda$
5.3	Space to different contact	3	$2\lambda$
5.4	Poly overlap of contact	2	$\lambda$
5.5	Poly overlap in direction of metal 1	2.5	$2\lambda$
5.6	Space to channel	3	$2\lambda$
5.7	Metal 1 overlap of contact	2	$\lambda$
5.8	Active overlap of contact	2	$\lambda$
5.9	p <sup>+</sup> select overlap of contact	3	$2\lambda$
5.10	Subs./well shorting contact, exactly	$3 \times 8$	$2\lambda \times 6\lambda$
6.	Metal 1 <sup>d</sup> (CIF Blue, Mask #7)		
6.1	Width	3	$2\lambda$
6.2	Spacing	4	$3\lambda$
6.3	Maximum current density	$0.8 \text{ mA}/\mu$	$0.8 \text{ mA}/\mu$

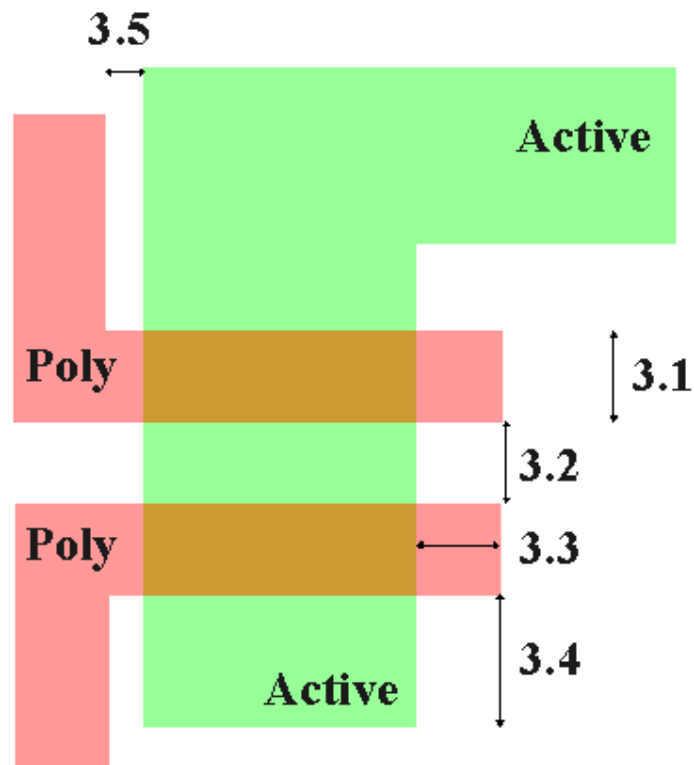
## Typical Design Rules (cont)

7.	Via <sup>e</sup> (CIF Purple Hatched, Mask #C1)		
7.1	Size, exactly	3 × 3	2λ × 2λ
7.2	Separation	3	2λ
7.3	Space to poly edge	4	2λ
7.4	Space to contact	3	2λ
7.5	Overlap by metal 1	2	λ
7.6	Overlap by metal 2	2	λ
7.7	Space to active edge	3	2λ
8.	Metal 2 (CIF Orange Hatched, Mask #C2)		
8.1	Width	5	3λ
8.2	Spacing	5	3λ
8.3	Bonding pad size	100 × 100	100 μ × 100 μ
8.4	Probe pad size	75 × 75	75 μ × 75 μ
8.5	Bonding pad separation	50	50 μ
8.6	Bonding to probe pad	30	30 μ
8.7	Probe pad separation	30	30 μ
8.8	Pad to circuitry	40	40 μ
8.9	Maximum current density	0.8 mA/μ	0.8 mA/μ
9.	Passivation <sup>f</sup> (CIF Purple Dashed, Mask #8)		
9.1	Bonding pad opening	90 × 90	90 μ × 90 μ
9.2	Probe pad opening	65 × 65	65 μ × 65 μ
10.	Metal 2 crossing coincident metal 1 and poly <sup>g</sup>		
10.1	Metal 1 to poly edge spacing when crossing metal 2	2	λ
10.2	Rule domain	2	λ
11.	Electrode (POLY II) <sup>h</sup> (CIF Purple Hatched, Mask #A1)		
11.1	Width	3	2λ
11.2	Spacing	3	2λ
11.3	POLY I overlap of POLY II	2	λ
11.4	Space to contact	3	2λ

## Typical Design Rules (cont)

### SCMOS Layout Rules - Poly

Rule	Description	Lambda		
		SCMOS	SUBM	DEEP
3.1	Minimum width	2	2	2
3.2	Minimum spacing over field	2	3	3
3.2.a	Minimum spacing over active	2	3	4
3.3	Minimum gate extension of active	2	2	2.5
3.4	Minimum active extension of poly	3	3	4
3.5	Minimum field poly to active	1	1	1



## Typical Process Description

### Process scenario of major process steps in typical p-well CMOS process<sup>a</sup>

1. Clean wafer
2. GROW THIN OXIDE
3. Apply photoresist
4. PATTERN P-WELL (MASK #1)
5. Develop photoresist
6. Deposit and diffuse p-type impurities
7. Strip photoresist
8. Strip thin oxide
9. Grow thin oxide
10. Apply layer of  $\text{Si}_3\text{N}_4$
11. Apply photoresist
12. PATTERN  $\text{Si}_3\text{N}_4$  (active area definition) (MASK #2)
13. Develop photoresist
14. Etch  $\text{Si}_3\text{N}_4$
15. Strip photoresist  
*Optional field threshold voltage adjust*
  - A.1 Apply photoresist
  - A.2 PATTERN ANTIMOAT IN SUBSTRATE (MASK #A1)
  - A.3 Develop photoresist
  - A.4 FIELD IMPLANT (n-type)
  - A.5 Strip photoresist
16. GROW FIELD OXIDE
17. Strip  $\text{Si}_3\text{N}_4$
18. Strip thin oxide
19. GROW GATE OXIDE
20. POLYSILICON DEPOSITION (POLY I)
21. Apply photoresist
22. PATTERN POLYSILICON (MASK #3)
23. Develop photoresist
24. ETCH POLYSILICON

## Typical Process Description (cont)

25. Strip photoresist  
*Optional steps for double polysilicon process*
  - B.1 Strip thin oxide
  - B.2 GROW THIN OXIDE
  - B.3 POLYSILICON DEPOSITION (POLY II)
  - B.4 Apply photoresist
  - B.5 PATTERN POLYSILICON (MASK #B1)
  - B.6 Develop photoresist
  - B.7 ETCH POLYSILICON
  - B.8 Strip photoresist
  - B.9 Strip thin oxide

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26. Apply photoresist
27. PATTERN P-CHANNEL DRAINS AND SOURCES AND P<sup>+</sup> GUARD RINGS (p-well ohmic contacts) (MASK #4)
28. Develop photoresist
29. p<sup>+</sup> IMPLANT
30. Strip photoresist
31. Apply photoresist
32. PATTERN N-CHANNEL DRAINS AND SOURCES AND N<sup>+</sup> GUARD RINGS (top ohmic contact to substrate) (MASK #5)
33. Develop photoresist
34. n<sup>+</sup> IMPLANT
35. Strip photoresist
36. Strip thin oxide
37. Grow oxide
38. Apply photoresist
39. PATTERN CONTACT OPENINGS (MASK #6)
40. Develop photoresist
41. Etch oxide
42. Strip photoresist
43. APPLY METAL
44. Apply photoresist
45. PATTERN METAL (MASK #7)
46. Develop photoresist
47. Etch metal

## Typical Process Description (cont)

- 48. Strip photoresist
  - Optional steps for double metal process*
  - C.1 Strip thin oxide
  - C.2 DEPOSIT INTERMETAL OXIDE
  - C.3 Apply photoresist
  - C.4 PATTERN VIAS (MASK #C1)
  - C.5 Develop photoresist
  - C.6 Etch oxide
  - C.7 Strip photoresist
  - C.8 APPLY METAL (Metal 2)
  - C.9 Apply photoresist
  - C.10 PATTERN METAL (MASK #C2)
  - C.11 Develop photoresist
  - C.12 Etch metal
  - C.13 Strip photoresist
- 49. APPLY PASSIVATION
- 50. Apply photoresist
- 51. PATTERN PAD OPENINGS (MASK #8)
- 52. Develop photoresist
- 53. Etch passivation
- 54. Strip photoresist
- 55. ASSEMBLE, PACKAGE AND TEST

# Typical Model Parameters

## Process parameters for a typical<sup>a</sup> p-well CMOS process

	Typical	Tolerance <sup>b</sup>	Units
<b>Square law model parameters</b>			
$V_{T0}$ (threshold voltage)			
n-channel ( $V_{TN0}$ )	0.75	$\pm 0.25$	V
p-channel ( $V_{TP0}$ )	-0.75	$\pm 0.25$	V
$K'$ (conduction factor)			
n-channel	24	$\pm 6$	$\mu\text{A}/\text{V}^2$
p-channel	8	$\pm 1.5$	$\mu\text{A}/\text{V}^2$
$\gamma$ (body effect)			
n-channel	0.8	$\pm 0.4$	$\text{V}^{1/2}$
p-channel	0.4	$\pm 0.2$	$\text{V}^{1/2}$
$\lambda$ (channel length modulation)			
n-channel	0.01	$\pm 50\%$	$\text{V}^{-1}$
p-channel	0.02	$\pm 50\%$	$\text{V}^{-1}$
$\phi$ (surface potential)			
n- and p-channel	0.6	$\pm 0.1$	V
<b>Process parameters</b>			
$\mu$ (channel mobility)			
n-channel	710		$\text{cm}^2/(\text{V} \cdot \text{s})$
p-channel	230		$\text{cm}^2/(\text{V} \cdot \text{s})$
<b>Doping<sup>c</sup></b>			
n <sup>+</sup> active	5	$\pm 4$	$10^{18}/\text{cm}^3$
p <sup>+</sup> active	5	$\pm 4$	$10^{17}/\text{cm}^3$
p-well	5	$\pm 2$	$10^{16}/\text{cm}^3$
n-substrate	1	$\pm 0.1$	$10^{16}/\text{cm}^3$

## Typical Model Parameters (cont)

<b>Physical feature sizes</b>			
$T_{\text{OX}}$ (gate oxide thickness)	500	$\pm 100$	Å
Total lateral diffusion			
n-channel	0.45	$\pm 0.15$	$\mu$
p-channel	0.6	$\pm 0.3$	$\mu$
Diffusion depth			
n <sup>+</sup> diffusion	0.45	$\pm 0.15$	$\mu$
p <sup>+</sup> diffusion	0.6	$\pm 0.3$	$\mu$
p-well	3.0	$\pm 30\%$	$\mu$
<b>Insulating layer separation</b>			
POLY I to POLY II	800	$\pm 100$	Å
Metal 1 to Substrate	1.55	$\pm 0.15$	$\mu$
Metal 1 to Diffusion	0.925	$\pm 0.25$	$\mu$
POLY I to Substrate (POLY I on field oxide)	0.75	$\pm 0.1$	$\mu$
Metal 1 to POLY I	0.87	$\pm 0.7$	$\mu$
Metal 2 to Substrate	2.7	$\pm 0.25$	$\mu$
Metal 2 to Metal I	1.2	$\pm 0.1$	$\mu$
Metal 2 to POLY I	2.0	$\pm 0.07$	$\mu$



## Typical Model Parameters (cont)

<b>Capacitances<sup>d</sup></b>			
$C_{OX}$ (gate oxide capacitance, n- and p-channel)	0.7	$\pm 0.1$	fF/ $\mu^2$
POLY I to substrate, poly in field	0.045	$\pm 0.01$	fF/ $\mu^2$
POLY II to substrate, poly in field	0.045	$\pm 0.01$	fF/ $\mu^2$
Metal 1 to substrate, metal in field	0.025	$\pm 0.005$	fF/ $\mu^2$
Metal 2 to substrate, metal in field	0.014	$\pm 0.002$	fF/ $\mu^2$
POLY I to POLY II	0.44	$\pm 0.05$	fF/ $\mu^2$
POLY I to Metal 1	0.04	$\pm 0.01$	fF/ $\mu^2$
POLY I to Metal 2	0.039	$\pm 0.003$	fF/ $\mu^2$
Metal 1 to Metal 2	0.035	$\pm 0.01$	fF/ $\mu^2$
Metal 1 to diffusion	0.04	$\pm 0.01$	fF/ $\mu^2$
Metal 2 to diffusion	0.02	$\pm 0.005$	fF/ $\mu^2$
n <sup>+</sup> diffusion to p-well (junction, bottom)	0.33	$\pm 0.17$	fF/ $\mu^2$
n <sup>+</sup> diffusion sidewall (junction, sidewall)	2.6	$\pm 0.6$	fF/ $\mu$
p <sup>+</sup> diffusion to substrate (junction, bottom)	0.38	$\pm 0.12$	fF/ $\mu^2$
p <sup>+</sup> diffusion sidewall (junction, sidewall)	3.5	$\pm 2.0$	fF/ $\mu$
p-well to substrate (junction, bottom)	0.2	$\pm 0.1$	fF/ $\mu^2$
p-well sidewall (junction, sidewall)	1.6	$\pm 1.0$	fF/ $\mu$
<b>Resistances</b>			
Substrate	25	$\pm 20\%$	$\Omega$ -cm
p-well	5000	$\pm 2500$	$\Omega/\square$
n <sup>+</sup> diffusion	35	$\pm 25$	$\Omega/\square$
p <sup>+</sup> diffusion	80	$\pm 55$	$\Omega/\square$
Metal	0.003	$\pm 25\%$	$\Omega/\square$
Poly	25	$\pm 25\%$	$\Omega/\square$
Metal 1–Metal 2 via ( $3 \mu \times 3 \mu$ contact)	<0.1		$\Omega$
Metal 1 contact to POLY I ( $3 \mu \times 3 \mu$ contact)	<10		$\Omega$
Metal 1 contact to n <sup>+</sup> or p <sup>+</sup> diffusion ( $3 \mu \times 3 \mu$ contact)	<5		$\Omega$

## Typical Model Parameters (cont)

### Breakdown voltages, leakage currents, migration currents and operating conditions

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Punchthrough voltages (Gate oxide, POLY I to POLY II)	>10	V
Diffusion reverse breakdown voltage	>10	V
p-well to substrate reverse breakdown voltage	>20	V
Metal 1 in field threshold voltage	>10	V
Metal 2 in field threshold voltage	>10	V
Poly-field threshold voltage	>10	V
Maximum operating voltage	7.0	V
n <sup>+</sup> diffusion to p-well leakage current	0.25	fA/ $\mu^2$
p <sup>+</sup> diffusion to substrate leakage current	0.25	fA/ $\mu^2$
p-well leakage current	0.25	fA/ $\mu^2$
Maximum metal current density	0.8	mA/ $\mu$ width
Maximum device operating temperature	200	°C

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## Typical Model Parameters (cont)

### Level 3 Model (n-ch and p-ch)

**SPICE MOSFET model parameters of a typical p-well CMOS process (MOSIS<sup>a</sup>)**

Parameter (Level 2 model)	n-channel	p-channel	Units
VTO	0.827	-0.895	V
KP	32.87	15.26	$\mu\text{A}/\text{V}^2$
GAMMA	1.36	0.879	$\text{V}^{1/2}$
PHI	0.6	0.6	V
LAMBDA	1.605E-2	4.709E-2	$\text{V}^{-1}$
CGSO	5.2E-4	4.0E-4	fF/ $\mu$ width
CGDO	5.2E-4	4.0E-4	fF/ $\mu$ width
RSH	25	95	$\Omega/\square$
CJ	3.2E-4	2.0E-4	$\rho \text{ fF}/\mu^2$
MJ	0.5	0.5	
CJSW	9.0E-4	4.5E-4	$\rho \text{ fF}/\mu$ perimeter
MJSW	0.33	0.33	
TOX	500	500	Å
NSUB	1.0E16	1.12E14	$1/\text{cm}^3$
NSS	0	0	$1/\text{cm}^2$
NFS	1.235E12	8.79E11	$1/\text{cm}^2$
TPG	1	-1	
XJ	0.4	0.4	$\mu$
LD	0.28	0.28	$\mu$
UO	200	100	$\text{cm}^2/(\text{V} \cdot \text{s})$
UCRIT	9.99E5	1.64E4	V/cm
UEXP	1.001E-3	0.1534	
VMAX	1.0E5	1.0E5	m/s
NEFF	1.001E-2	1.001E-2	
DELTA	1.2405	1.938	

## Typical Model Parameters (cont)

```
.MODEL CMOSN NMOS (  
+VERSION = 3.1  
+XJ      = 1.5E-7  
+K1      = 0.875093  
+K3B     = -8.5140476  
+DVTOW   = 0  
+DVTO    = 2.670658  
+UO      = 452.3081836  
+UC      = 1.166279E-11  
+AGS     = 0.1384489  
+KETA    = -3.615287E-3  
+RDSW    = 1.380341E3  
+WR      = 1  
+XL      = 1E-7  
+DWB     = 3.537786E-8  
+CIT     = 0  
+CDSCB   = 0  
+DSUB    = 0.076309  
+PDIBLC2 = 2.23243E-3  
+PSCBE1  = 6.619472E8  
+DELTA   = 0.01  
+PRT     = 0  
+KT1L    = 0  
+UB1     = -7.61E-18  
+WL      = 0  
+WWN     = 1  
+LLN     = 1  
+LWL     = 0  
+CGDO    = 2.34E-10  
+CJ      = 4.240724E-4  
+CJSW    = 3.007134E-10  
+CJSWG   = 1.64E-10  
+CF      = 0  
+PK2     = -0.0283027
```

## BSIM 4 Model (n-ch)

```
TNOM      = 27  
NCH       = 1.7E17  
K2        = -0.0943223  
WO        = 1.01582E-8  
DVT1W    = 0  
DVT1     = 0.4282172  
UA        = 3.061716E-13  
VSAT     = 1.682414E5  
BO        = 2.579158E-6  
A1        = 1.054571E-6  
PRWG     = 0.0301426  
WINT     = 2.594349E-7  
XW       = 0  
VOFF     = 0  
CDSC     = 2.4E-4  
ETAO     = 2.332015E-3  
PCLM     = 2.6209353  
PDIBLCB  = -0.0436947  
PSCBE2   = 2.968801E-4  
RSH      = 80.9  
UTE      = -1.5  
KT2      = 0.022  
UC1      = -5.6E-11  
WLN      = 1  
WWL      = 0  
LW       = 0  
CAPMOD   = 2  
CGSO     = 2.34E-10  
PB       = 0.9148626  
PBSW     = 0.8  
PBSWG    = 0.8  
PVTHO    = 0.0526696  
WKETA    = -0.0191754  
LEVEL    = 49  
TOX      = 1.4E-8  
VTHO     = 0.6656437  
K3       = 25.0562441  
NLX      = 1E-9  
DVT2W    = 0  
DVT2     = -0.1373089  
UB       = 1.515137E-18  
AO       = 0.6297744  
B1       = 5E-6  
A2       = 0.3379035  
PRWB     = 0.0106493  
LINT     = 7.489566E-8  
DWG      = -9.471353E-9  
NFACTOR  = 1.0754804  
CDSCD    = 0  
ETAB     = -1.531255E-4  
PDIBLC1  = 1  
DROUT    = 1.0300278  
PVAG     = 9.970995E-3  
MOBMOD   = 1  
KT1      = -0.11  
UA1      = 4.31E-9  
AT       = 3.3E4  
WW       = 0  
LL       = 0  
LWN      = 1  
XPART    = 0.5  
CGBO     = 1E-9  
MJ       = 0.4416777  
MJSW     = 0.2025106  
MJSWG    = 0.2025106  
PRDSW    = 110.1539295  
LKETA    = 8.469064E-4
```

98 parameters in this BSIM Model !

# Typical Model Parameters (cont)

## BSIM 4 Model (p-ch)

```

.MODEL CMOSF PMOS (
+VERSION = 3.1          TNOM    = 27          LEVEL  = 49
+XJ      = 1.5E-7       NCH    = 1.7E17       TOX    = 1.4E-8
+K1      = 0.5600277    K2     = 9.302429E-3  VTH0   = -0.9633249
+K3B     = -1.0103515   WO     = 1.010628E-8  K3     = 7.2192028
+DVTOW   = 0           DVT1W  = 0           NLX    = 5.826683E-8
+DVTO    = 2.2199372   DVT1   = 0.5378964   DVT2W  = 0
+UO      = 220.5729225  UA     = 3.141811E-9  DVT2   = -0.1158128
+UC      = -5.76898E-11 VSAT   = 1.342779E5   UB     = 1.085892E-21
+AGS     = 0.157364    BO     = 9.735259E-7  AO     = 0.9333822
+KETA    = -2.42686E-3 A1     = 3.447019E-4  B1     = 5E-6
+RDSW    = 3E3         PRWG   = -0.0418484  A2     = 0.3701317
+WR      = 1           WINT   = 3.097872E-7 PRWB   = -0.0212357
+XL      = 1E-7        XW     = 0           LINT   = 1.040878E-7
+DWB     = 1.629532E-8 VOFF   = -0.0823738  DWG    = -1.983686E-8
+CIT     = 0           CDSC   = 2.4E-4       NFACTOR = 0.969384
+CDSCB   = 0          ETAO   = 0.4985496    CDSCD  = 0
+DSUB    = 1          PCLM   = 2.1142057    ETAB   = -0.0653358
+PDIBLC2 = 3.172604E-3 PDIBLCB = -0.0511673  PDIBLC1 = 0.0256688
+PSCBE1  = 1.851867E10 PSCBE2 = 1.697939E-9  DROUT  = 0.1695622
+DELTA   = 0.01       RSH    = 103.6       PVAG   = 0
+PRT     = 0          UTE    = -1.5        MOBMOD = 1
+KT1L    = 0          KT2    = 0.022       KT1    = -0.11
+UB1     = -7.61E-18  UC1    = -5.6E-11   UA1    = 4.31E-9
+WL      = 0          WLN    = 1           AT     = 3.3E4
+WWN     = 1          WWL    = 0          WW     = 0
+LLN     = 1          LWL    = 0          LL     = 0
+LWL     = 0          CAPMOD = 2          LWN    = 1
+CGDO    = 3.09E-10   CGSO   = 3.09E-10   XPART  = 0.5
+CJ      = 7.410008E-4 PB      = 0.9665307  CGBO   = 1E-9
+CJSW    = 2.487127E-10 PBSW   = 0.99        MJ     = 0.4978642
+CJSWG   = 6.4E-11   PBSWG  = 0.99        MJSW   = 0.3877813
+CF      = 0          PVTHO  = 5.98016E-3  MJSWG  = 0.3877813
+PK2     = 3.73981E-3 WKETA   = 2.870507E-3 PRDSW  = 14.8598424

```

-

# Technology Files

- • **Design Rules**
- **Process Flow (Fabrication Technology)** (will discuss next )
- **Model Parameters** (will discuss in substantially more detail after device operation and more advanced models are introduced)

# Design Rules

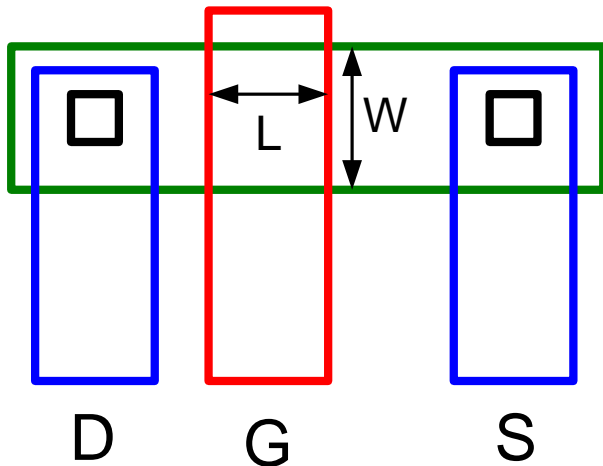
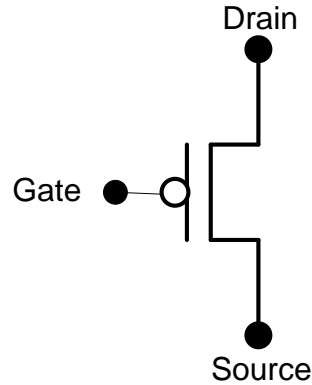
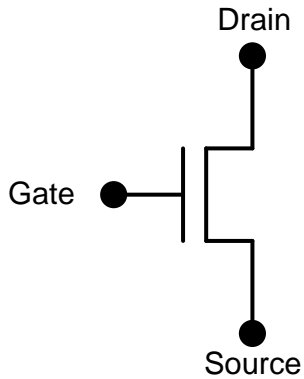
- Give minimum feature sizes, spacing, and other constraints that are acceptable in a process
- Very large number of devices can be reliably made with the design rules of a process
- Yield and performance unpredictable and often low if rules are violated
- Compatible with design rule checker in integrated toolsets

# Design Rules and Layout – consider transistors

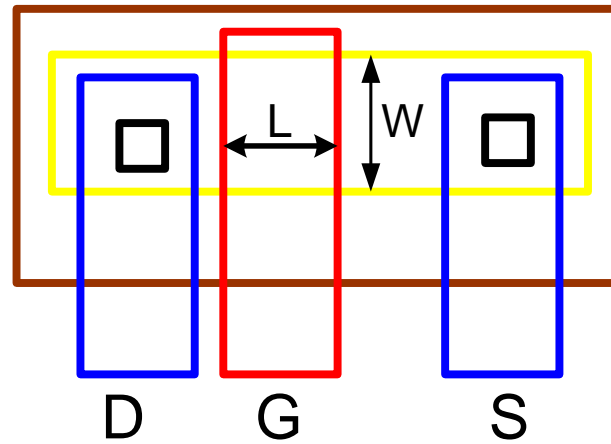
## Layer Map

n-well bulk CMOS Process

- p-active
- n-active
- Poly 1
- Metal 1
- n-well
- contact



Layout

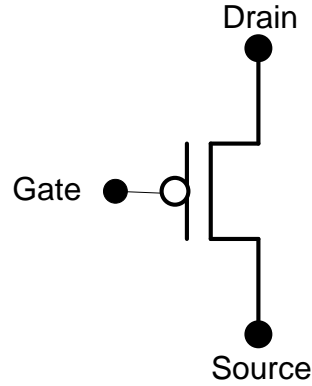
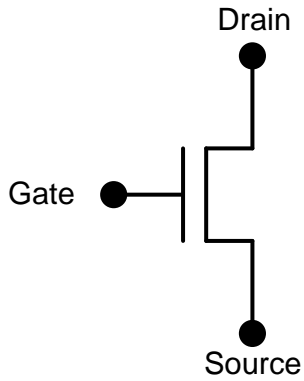


Layout







Layout always represented in a top view in two dimensions

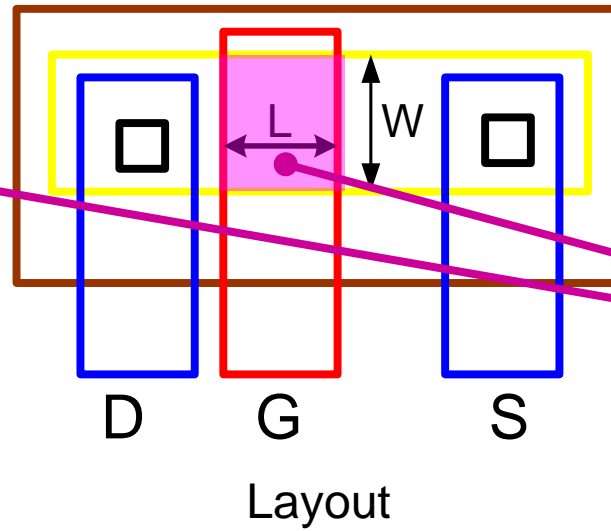
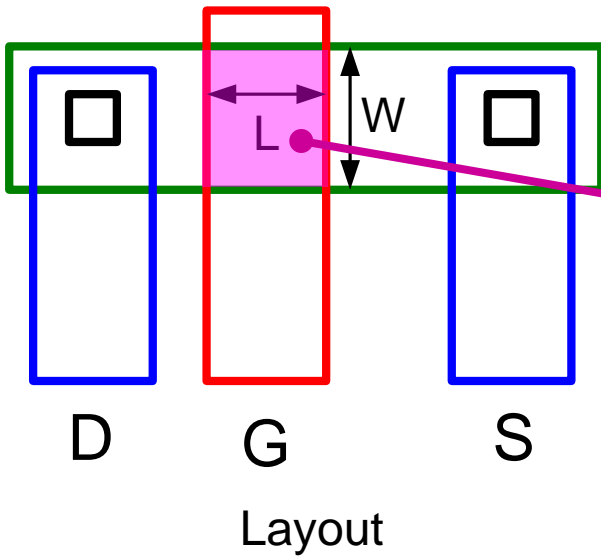


# Design Rules and Layout – consider transistors



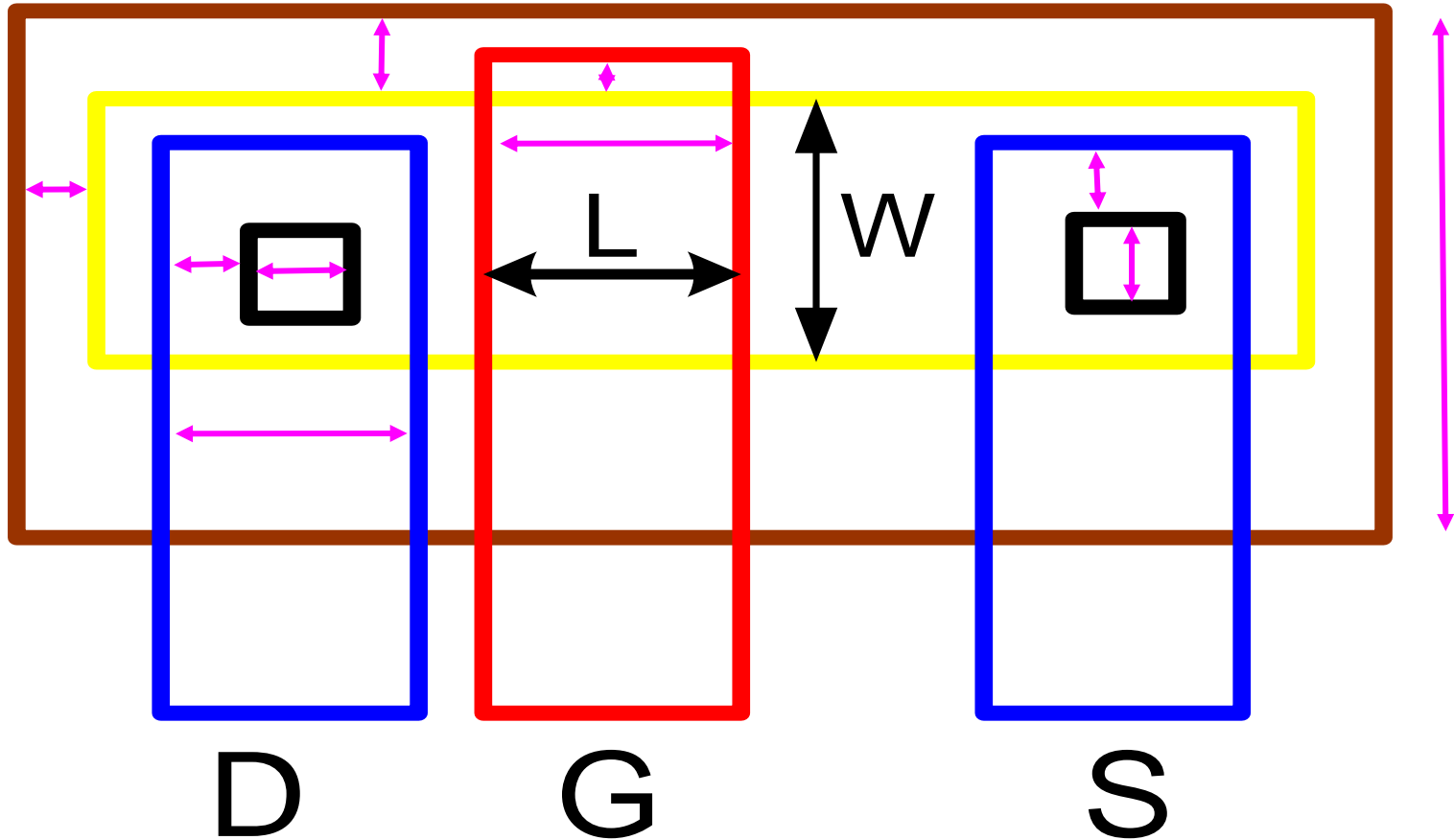
## Layer Map

-  p-active
-  n-active
-  Poly 1
-  Metal 1
-  n-well
-  contact



Everything useful in channel region. All other features just overhead that degrades performance

# Design Rules

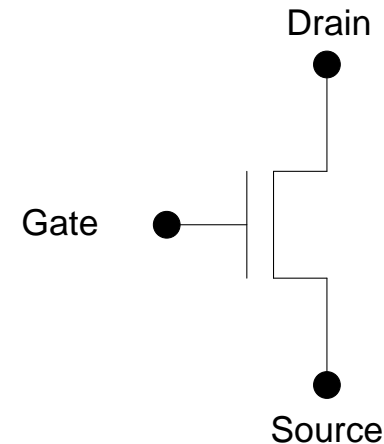
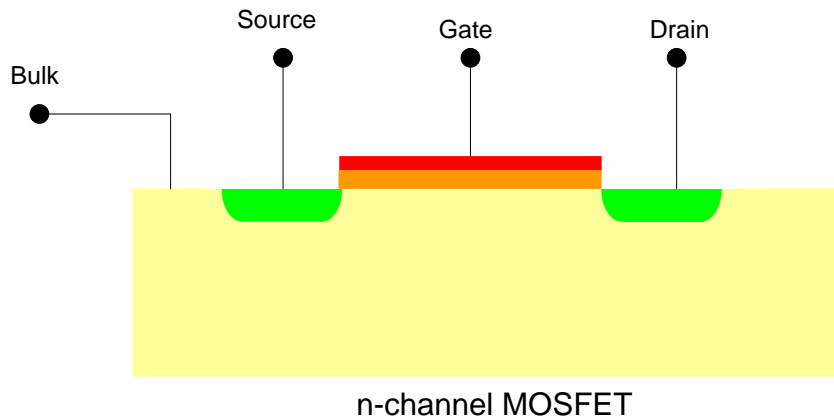


Design rules give minimum feature sizes and spacings

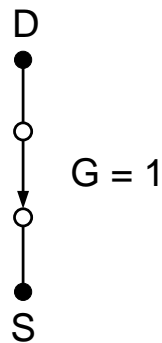
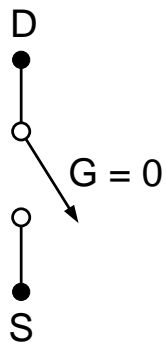
Designers generally do layouts to minimize size of circuit subject to design rule constraints (because yield, cost, and performance usually improve)

# MOS Transistor

## Qualitative Discussion of n-channel Operation



### Equivalent Circuit for n-channel MOSFET

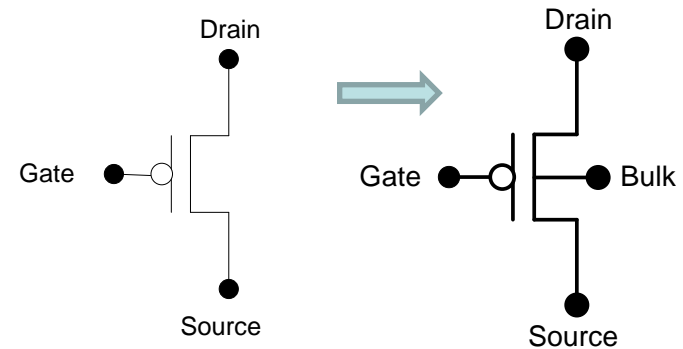
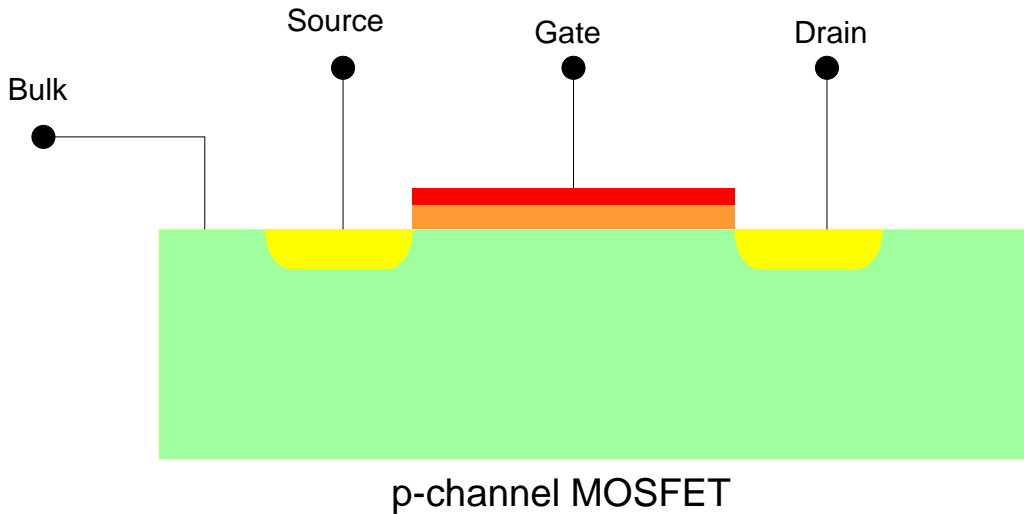
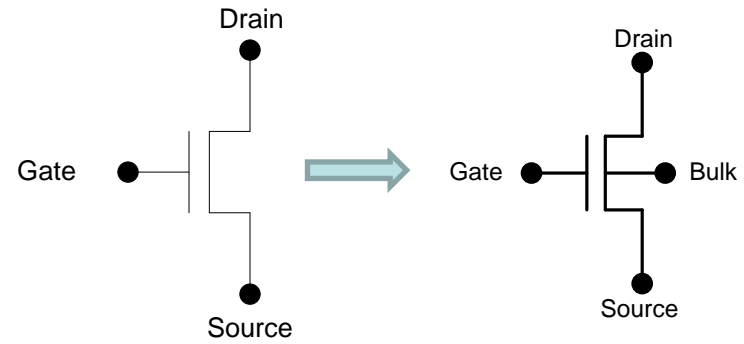
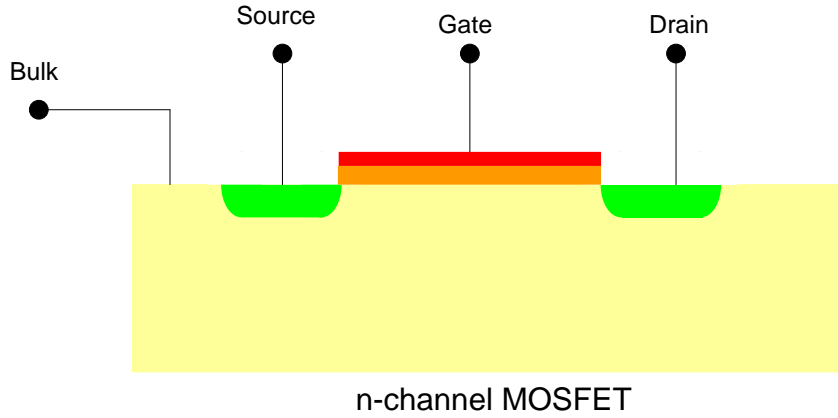


- Source assumed connected to (or close to) ground
- $V_{GS}=0$  denoted as Boolean gate voltage  $G=0$
- $V_{GS}=V_{DD}$  denoted as Boolean gate voltage  $G=1$
- Boolean  $G$  is relative to ground potential

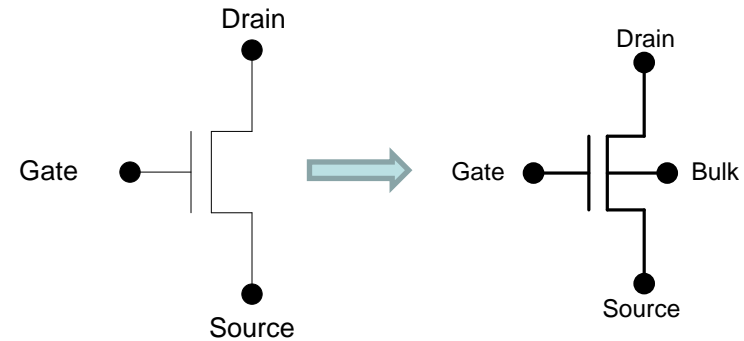
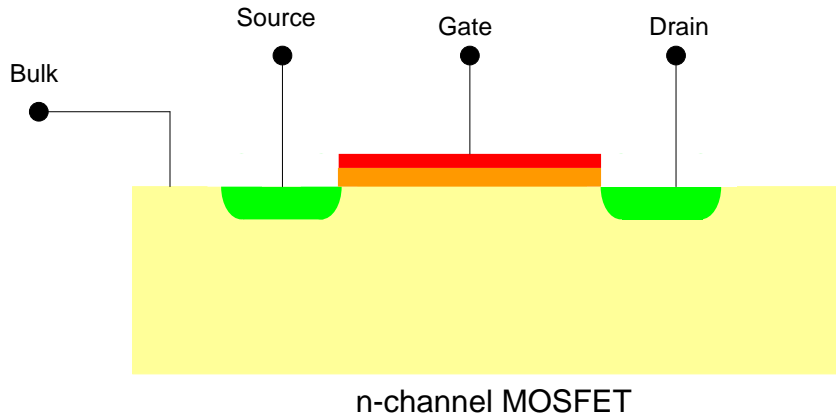
This is the first model we have for the n-channel MOSFET !

Ideal switch-level model

# MOS Transistor



# MOS Transistor Nomenclature



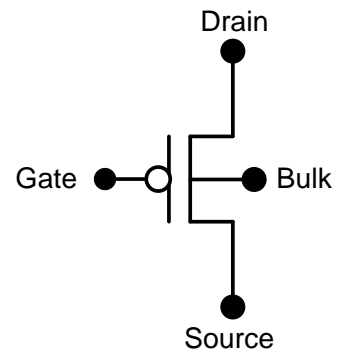
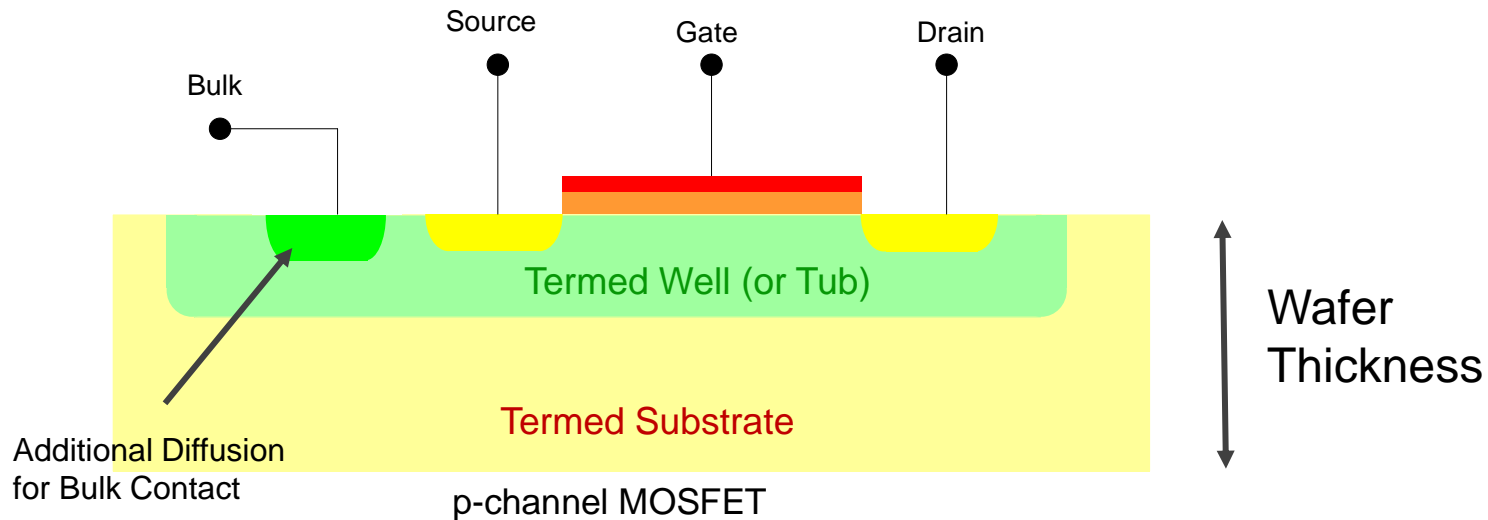
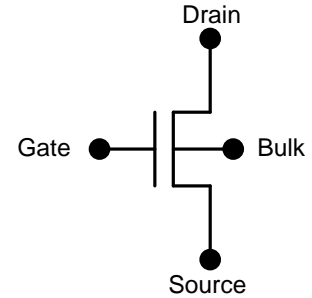
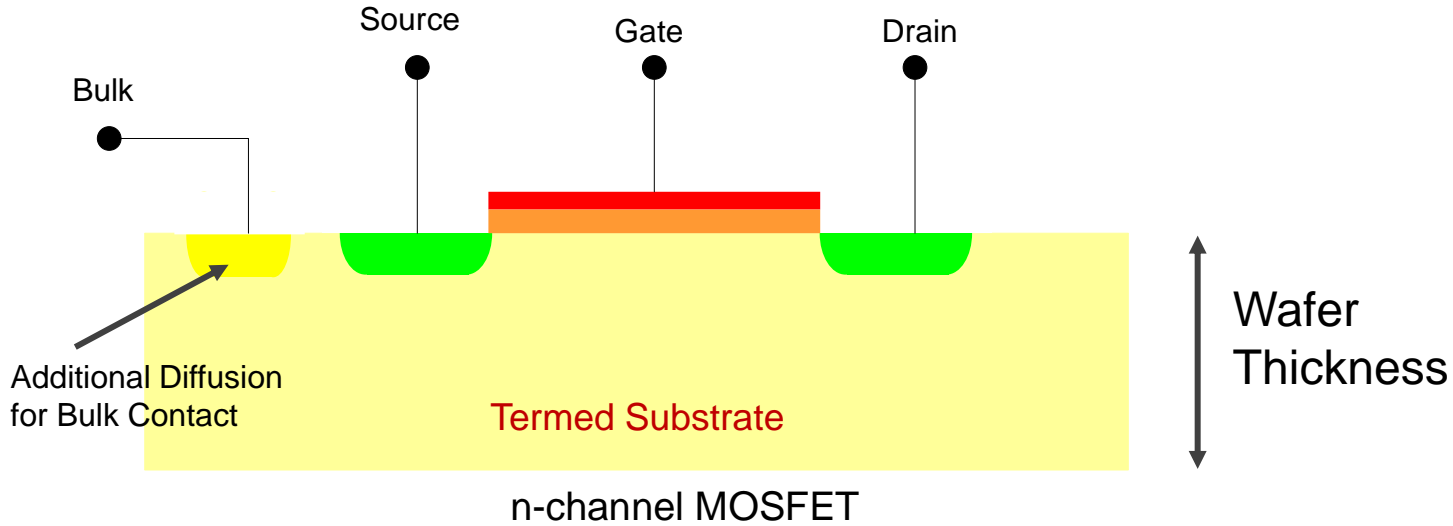
Metal Oxide Semiconductor



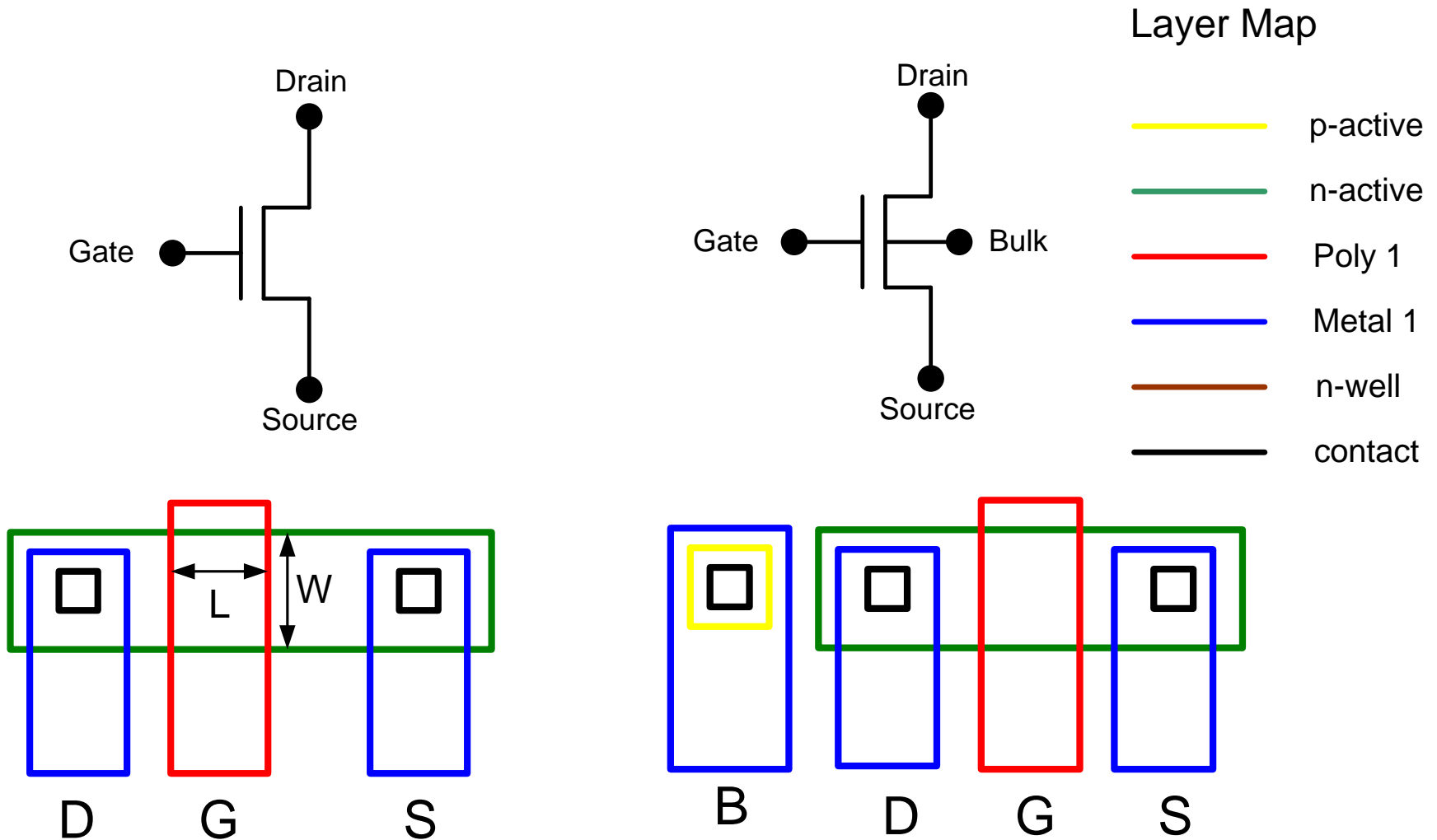
MOS

Early processes used metal for the gate, today metal is seldom used but the term MOS transistor is standard even though the gate is no longer metal

# MOS Transistor in Bulk CMOS Process

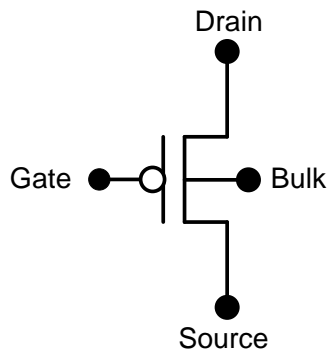
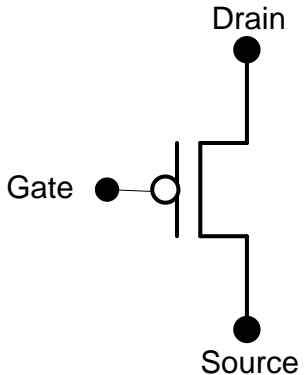


# Design Rules and Layout – consider transistors



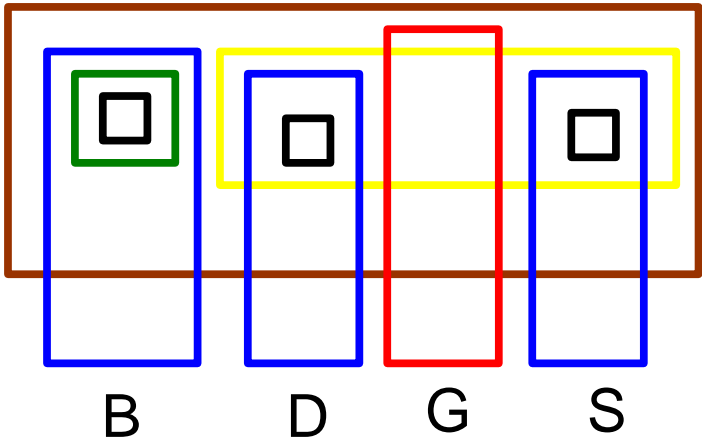
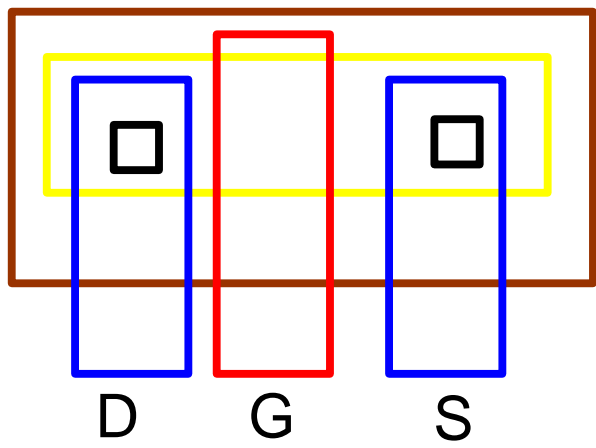
- Bulk connection needed
- Single bulk connection can often be used for several (many) transistors

# Design Rules and Layout – consider transistors



## Layer Map

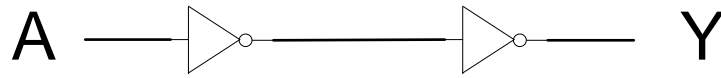
- p-active
- n-active
- Poly 1
- Metal 1
- n-well
- contact



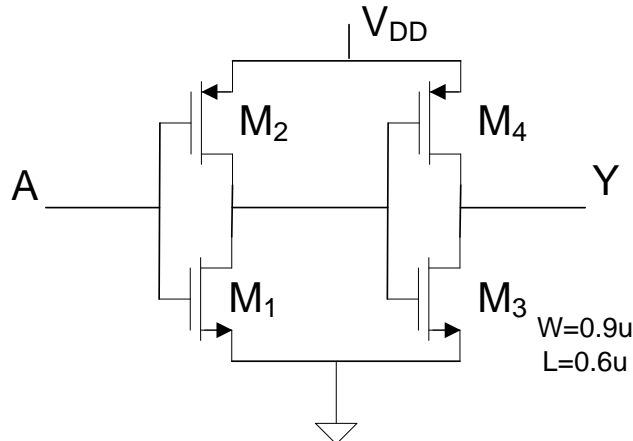
- Bulk connection needed
- Single bulk connection can often be used for several (many) transistors if they share the same well



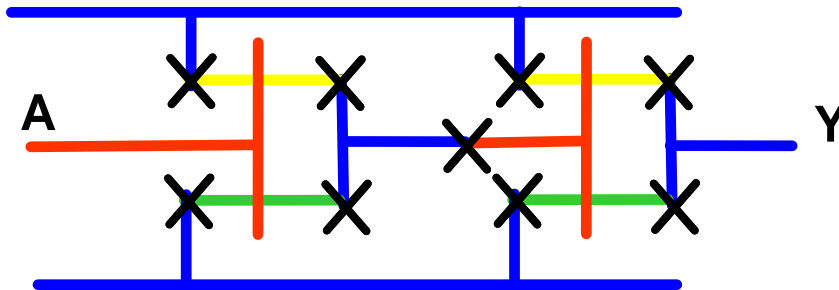
# Design Rules and Layout (example)



Logic Circuit

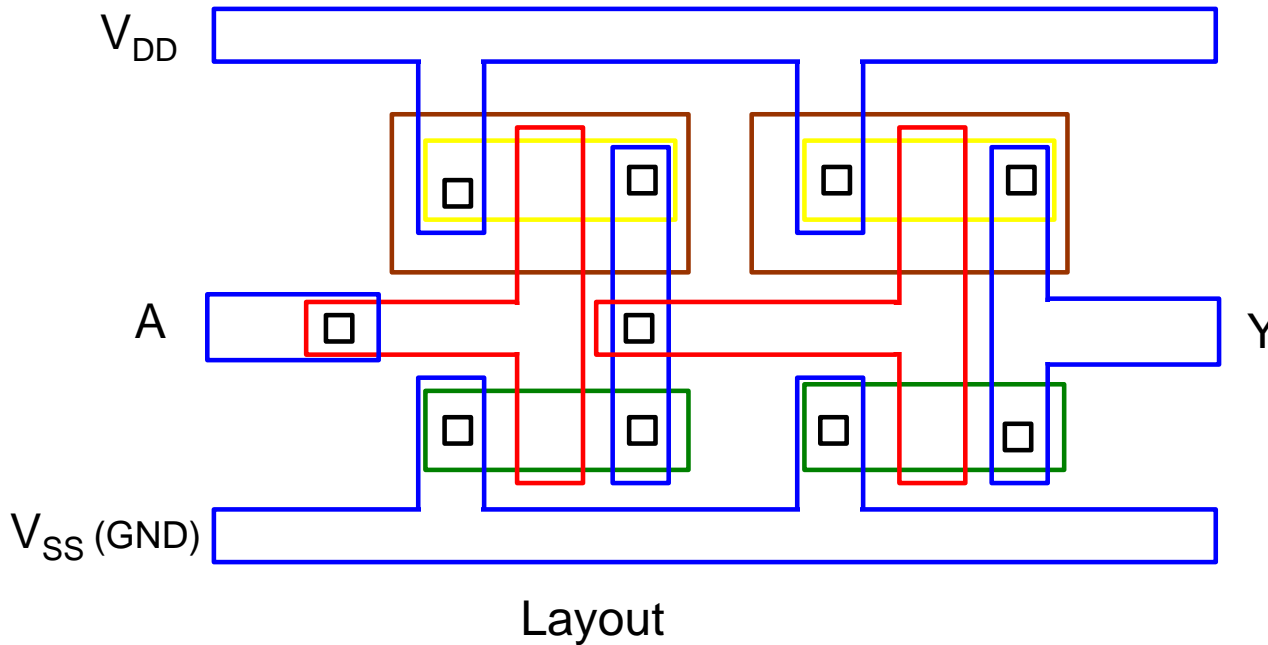
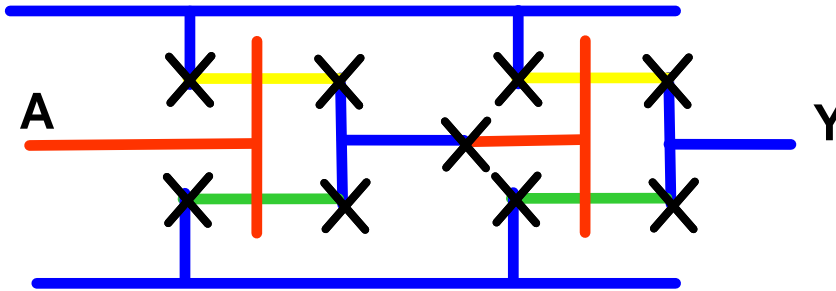


Circuit Schematic (Including Device Sizing)









Stick Diagram

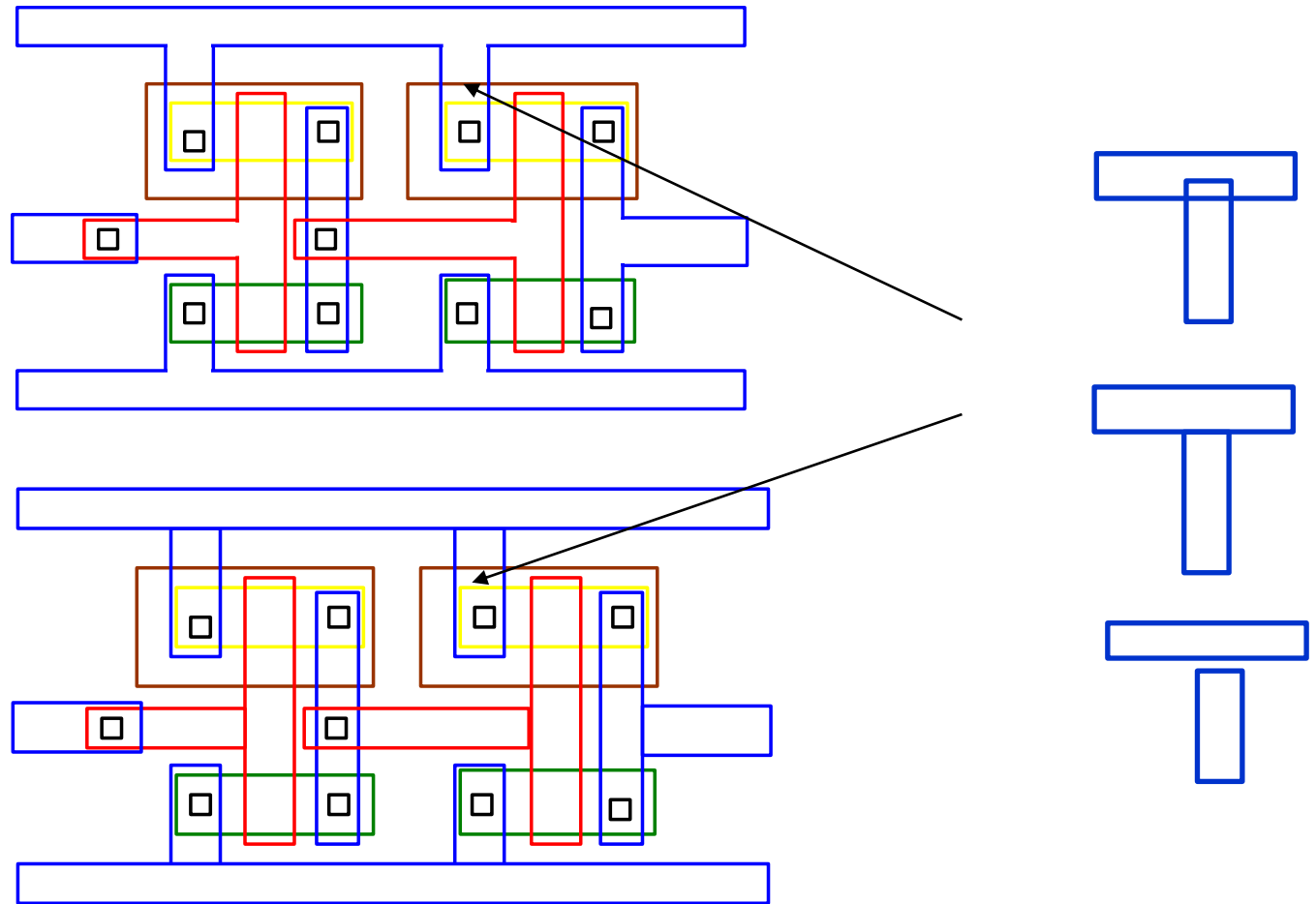
# Design Rules (example)



## Layer Map

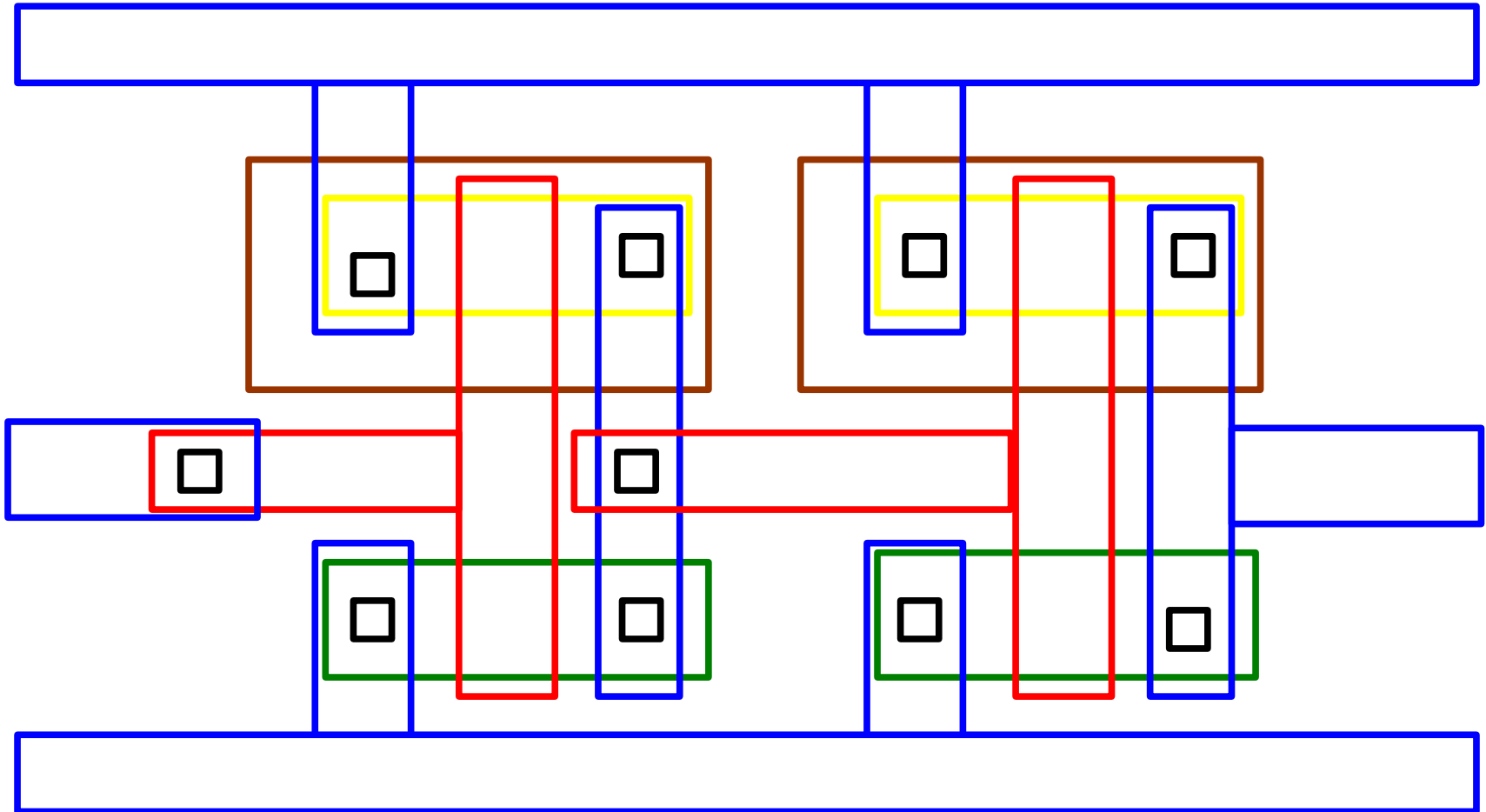
-  p-active
-  n-active
-  Poly 1
-  Metal 1
-  n-well
-  contact

# Design Rules (example)



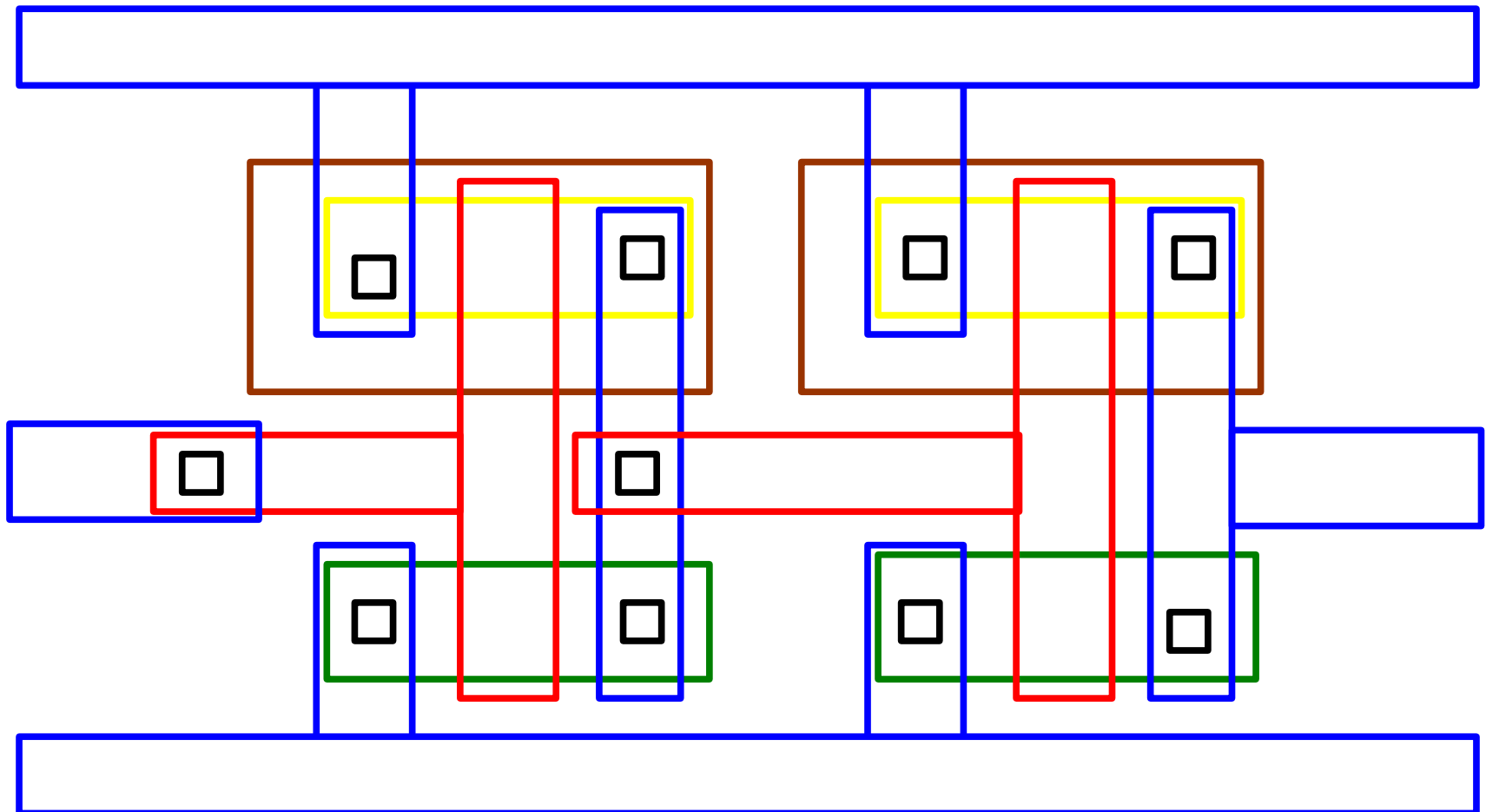
- Polygons in Geometric Description File (GDF) merged (when driving the pattern generator that makes the masks)
- Separate rectangles generally more convenient to represent
- Good practice to overlap rectangles to avoid break (though such an error would likely be caught with DRC)

# Design Rules (example)



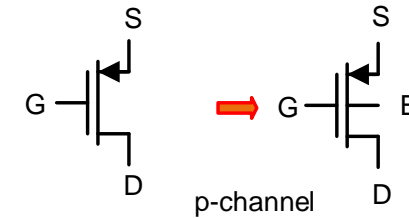
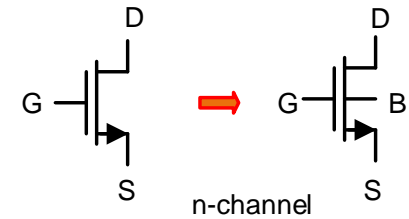
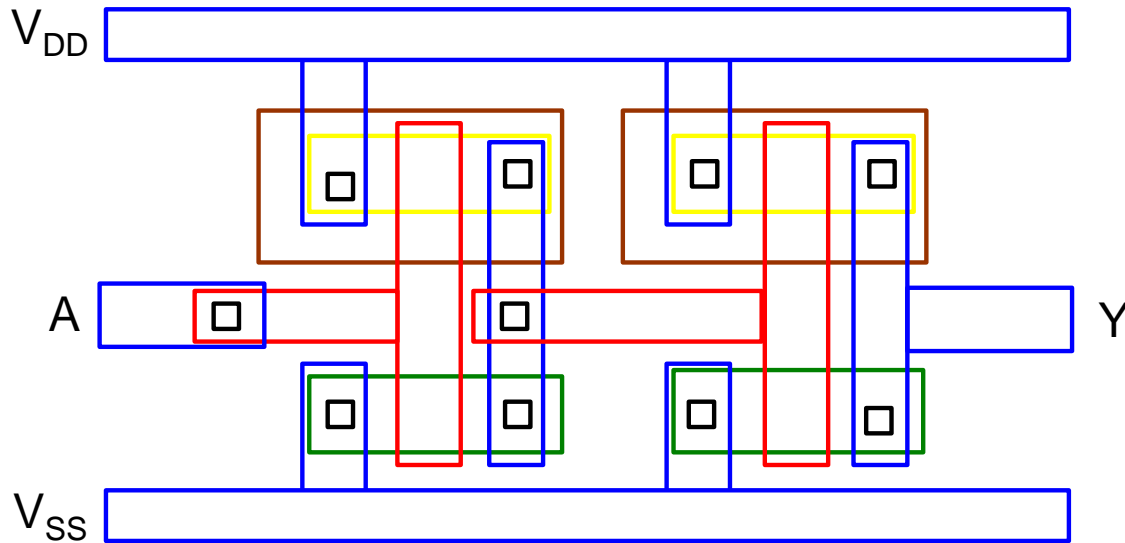
- Design rules must be satisfied throughout the design
- DRC runs incrementally during layout in most existing tools to flag most problems
- DRC can catch layout design rule errors but not circuit connection errors

# Design Rules (example)



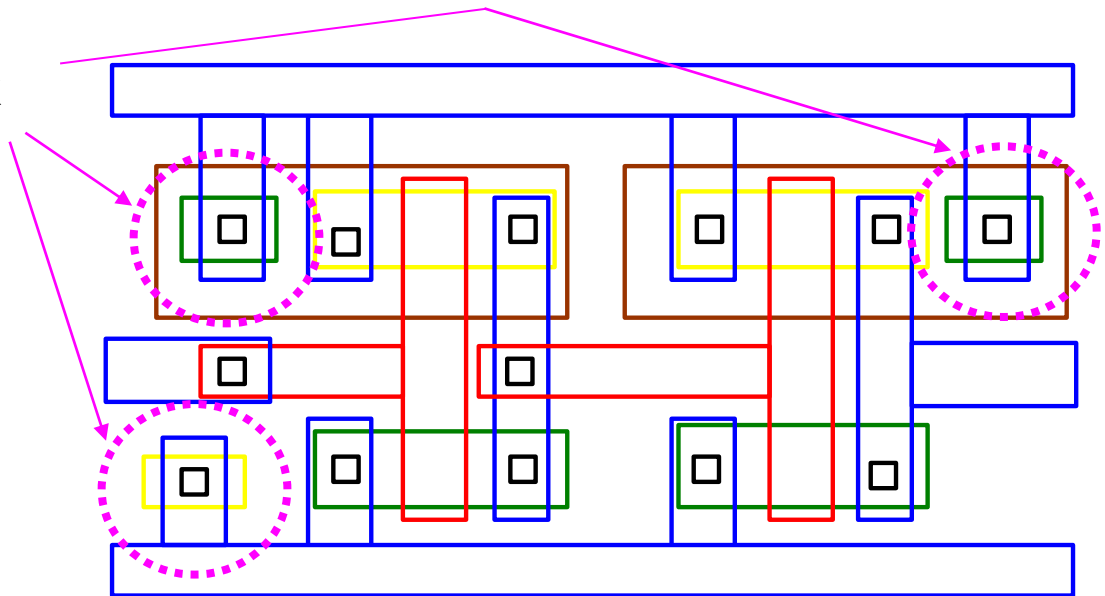
What is wrong with this layout ?  
Bulk connections missing!

# Design Rules (example)

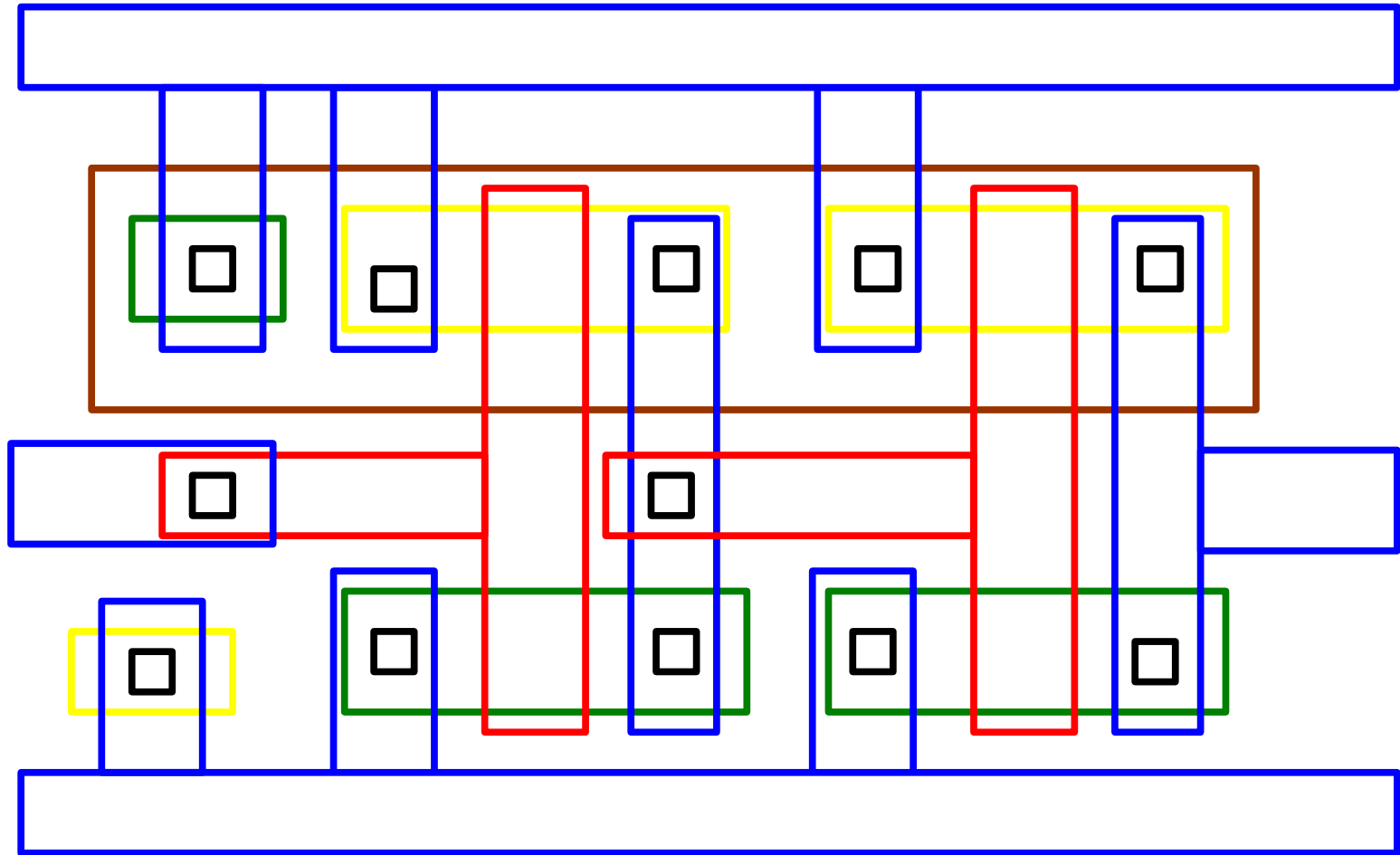


Actually 4-terminal device

- Note diffusions needed for bulk connections
- Note n-well connections increase area a significant amount
- Note n-wells are both connected to  $V_{DD}$  in this circuit

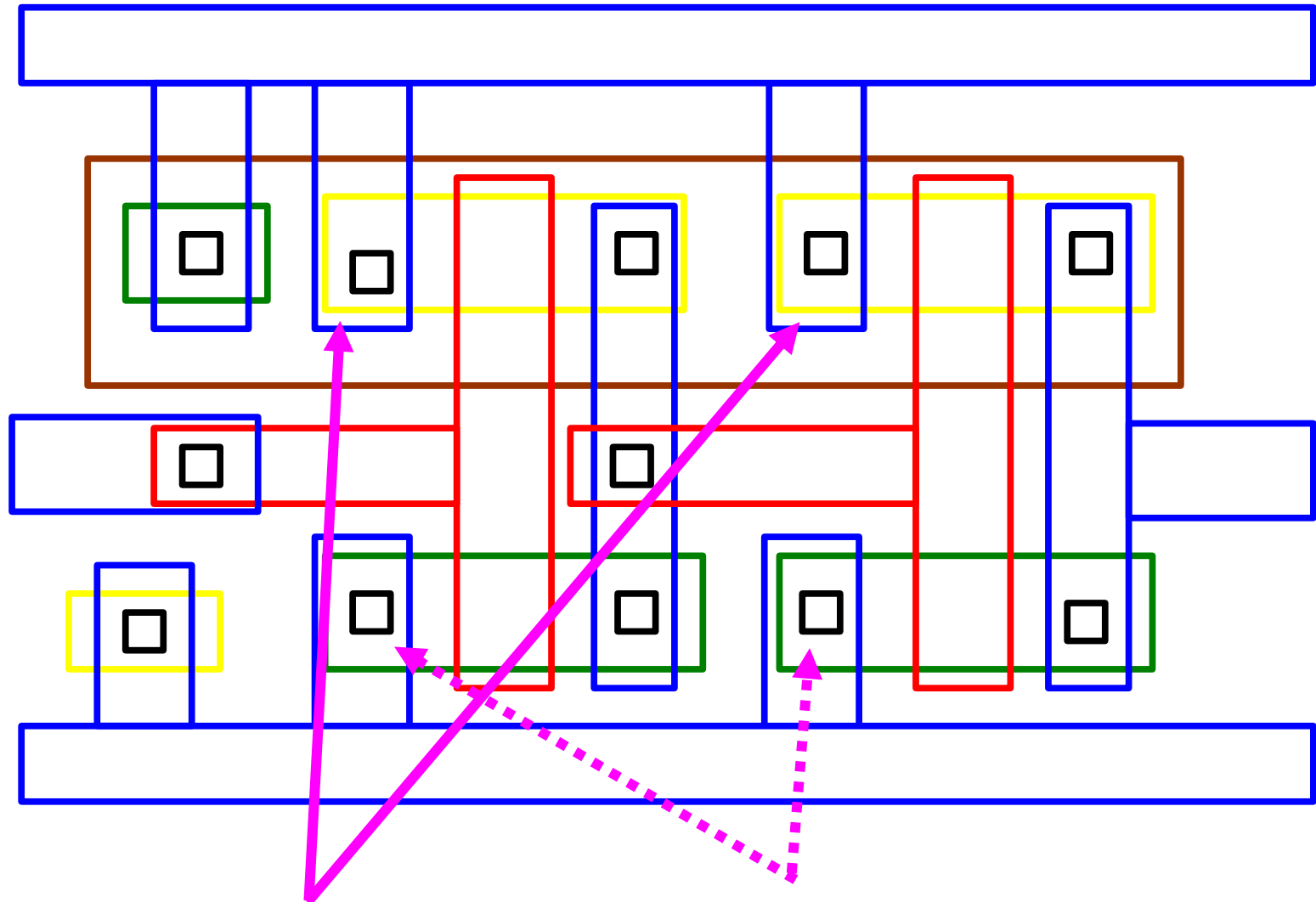


# Design Rules (example)



Layout with shared p-well reduces area

# Design Rules (example)



Shared p-active can be combined to reduce area

Shared n-active can be combined to reduce area



# Design Rules

- Design rules can be given in absolute dimensions for every rule
- Design rules can be parameterized and given relative to a parameter
  - Makes movement from one process to another more convenient
  - Easier for designer to remember
  - Some penalty in area efficiency
  - Often termed  $\lambda$ -based design rules
  - Typically  $\lambda$  is  $\frac{1}{2}$  the minimum feature size in a process

# Design Rules

- See [www.MOSIS.com](http://www.MOSIS.com) for design rules
- Some of these files are on class WEB site
  - SCMOS Rules Updated Sept 2005.pdf
  - Mosis Rules Pictorial.pdf



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*MOSIS is pleased to announce a collaboration with the **Intel Custom Foundry**. MOSIS is committed to providing foundry access to key technologies for our customers. The primary Foundries which The MOSIS Service supports are TSMC, GlobalFoundries, Intel and On Semi. Please see the Intel collaboration **press release**.*

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## MOSIS Products & Services



Behind MOSIS is a service infrastructure equipped to deliver a full range of products to today's ambitious IC designers – worldwide.

Through our trusted partnerships with top foundries, customers can access cutting-edge technologies and manufacturing solutions that span all parts of the production cycle.

Our technical experts make the process simple, efficient and less time-intensive. From small to large-quantity fabrication runs, to packaging and assembly, our portfolio is optimized for flexibility and tailored to meet the unique production needs of our diverse customers.

### PRODUCTS

#### Multi-Project Wafer (MPW) Runs

This "shared mask" model combines on one mask set designs from multiple customers or diverse designs from a single company.

#### Dedicated Runs

Dedicated (COT, or Customer Owned Tooling) runs through MOSIS are also available. Dedicated runs can be scheduled to start at any time.

#### Prices and Quotes

Costs for fabrication, packaging and assembly services are available online.

### FABRICATION PROCESSES

**GlobalFoundries** featured processes:

CMOS: 12 nm, 22 FD<sub>X</sub>, 45 RF<sub>SOI</sub>, 55 nm, 9HP (90 nm), 9WG (90 nm), 8HP (0.13 μm), 8XP (0.13 μm), 7WL (0.18 μm) and 7SW (0.18 μm).

**TSMC** featured processes:

28 nm, 40 nm, 65 nm and 180 nm.

**ON Semi** featured CMOS processes

C5 (0.5 μm) CMOS





Events > Products & Services > Fab Processes > ON Semiconductor > ON Semi 0.50 Micron B5 Process

## B5 Process

ON Semiconductor (formerly AMIS) 0.50 Micron



### Process Family Description

This non-silicided CMOS process has 3 metal layers and 2 poly layers, and a high resistance layer. Stacked contacts are supported. The process is for 5 volt applications. MOSIS orders EPI wafers for this process. Non-EPI (bulk) is an additional cost option and not available for MEP submissions. For further information, see the [ON Semiconductor Foundry Mixed-Signal Offerings](#) web page.

### B5N Process

PIP (poly2 over poly) capacitors (950 aF/μm<sup>2</sup>) and the HRP (High Resistance) option are available on multiproject runs.

### B5F Process

The B5F process offers the above layers of C5N plus Thick\_Gate, N\_Minus\_Implant (Npblk), and P\_Minus\_Implant (Ppblk).

### Design Rules

This process supports the following design rules.

Design Rules	Lambda <sup>1</sup>	Feature Size <sup>1</sup>	Availability
ON Semi B5F/N Rules	n/a	0.60	MOSIS, ON Semiconductor
SCMOS_SUBM	0.30	0.60	MOSIS in PDF
SCMOS	0.35	0.60 (after sizing)	MOSIS in PDF

<sup>1</sup>Values in micrometers (μm)

Review the [CMP and antenna guidelines](#) which apply to both sets of design rules. MOSIS Technology Codes See [Technology Codes for ON Semiconductor B5F/N Process](#).

This will take you to a 54 page pdf file that can be downloaded

## Examples in slides

Table 2a: MOSIS SCMOS-Compatible Mappings

Foundry	Process	Lambda (micro- meters)	Options
ON Semi	C5F/N (0.5 micron <i>n</i> -well)	0.35	<u>SCN3M</u> , <u>SCN3ME</u>
TSMC	0.35 micron 2P4M (4 Metal Polycided, 3.3 V/5 V)	0.25	<u>SCN4ME</u>
TSMC	0.35 micron 1P4M (4 Metal Silicided, 3.3 V/5 V)	0.25	<u>SCN4M</u>

Table 2b: MOSIS SCMOS\_SUBM-Compatible Mappings

Foundry	Process	Lambda (micro- meters)	Options
ON Semi	C5F/N (0.5 micron <i>n</i> -well)	0.30	<u>SCN3M SUBM</u> , <u>SCN3ME SUBM</u>
TSMC	0.35 micron 2P4M (4 Metal Polycided, 3.3 V/5 V)	0.20	<u>SCN4ME SUBM</u>
TSMC	0.35 micron 1P4M (4 Metal Silicided, 3.3 V/5 V)	0.20	<u>SCN4M SUBM</u>
TSMC	0.25 micron 5 Metal 1 Poly (2.5 V/3.3 V)	0.15	<u>SCN5M SUBM</u>
TSMC	0.18 micron 6 Metal 1 Poly (1.8 V/3.3 V)	0.10	<u>SCN6M SUBM</u>

Table 2c: MOSIS SCMOS\_DEEP-Compatible Mappings

Foundry	Process	Lambda (micro- meters)	Options
TSMC	0.25 micron 5 Metal 1 Poly (2.5 V/3.3 V)	0.12	<u>SCN5M DEEP</u>
TSMC	0.18 micron 6 Metal 1 Poly (1.8 V/3.3 V)	0.09	<u>SCN6M DEEP</u>

Our labs and class projects

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## 2.1. Well Type

The Scalable CMOS (SC) rules support both  $n$ -well and  $p$ -well processes. MOSIS recognizes three base technology codes that let the designer specify the well type of the process selected. SCN specifies an  $n$ -well process, SCP specifies a  $p$ -well process, and SCE indicates that the designer is willing to utilize a process of either  $n$ -well or  $p$ -well.

An SCE design must provide both a drawn  $n$ -well and a drawn  $p$ -well; MOSIS will use the well that corresponds to the selected process and ignore the other well. As a convenience, SCN and SCP designs may also include the other well ( $p$ -well in an SCN design or  $n$ -well in an SCP design), but it will always be ignored.

MOSIS currently offers only  $n$ -well processes or foundry-designated twin-well processes that from the design and process flow standpoints are equivalent to  $n$ -well processes. These twin-well processes may have options (deep  $n$ -well) that provide independently isolated  $p$ -wells. For all of these processes at this time use the technology code SCN. SCP is currently not supported, and SCE is treated exactly as SCN.

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## 2.2. SCMOS Options

SCMOS options are used to designate projects that use additional layers beyond the standard single-poly, double metal CMOS. Each option is called out with a designator that is appended to the basic technology-code. Please note that not all possible combinations are available. The current list is shown in Table 1.

MOSIS has not issued SCMOS design rules for some vendor-supported options. For example, any designer using the SCMOS rules who wants the TSMC Thick\_Top\_Metal must draw the top metal to comply with the TSMC rules for that layer. Questions about other non-SCMOS layers should be directed to [support@mosis.com](mailto:support@mosis.com).

Table 1: SCMOS Technology Options

Designation	Long Form	Description
E	Electrode	Adds a second polysilicon layer (poly2) that can serve either as the upper electrode of a poly capacitor or (1.5 micron only) as a gate for transistors
A	Analog	Adds electrode (as in E option), plus layers for vertical NPN transistor pbase
3M	3 Metal	Adds second via (via2) and third metal (metal3) layers
4M	4 Metal	Adds 3M plus third via (via3) and fourth metal (metal4) layers
5M	5 Metal	Adds 4M plus fourth via (via4) and fifth metal (metal5) layers
6M	6 Metal	Adds 5M plus fifth via (via5) and sixth metal (metal6) layers
LC	Linear Capacitor	Adds a cap_well layer for linear capacitors
PC	Poly Cap	Adds poly_cap, a different layer for linear capacitors
SUBM	Sub-Micron	Uses revised layout rules for better fit to sub-micron processes ( <a href="#">see section 2.4</a> )
DEEP	Deep	Uses revised layout rules for better fit to deep sub-micron processes ( <a href="#">see section 2.4</a> )



Table 5: Technology-code Map

Technology code with link to layer map	Layers
<u>SCNE</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNA</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Pbase</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNPC</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly_cap</u> , <u>Poly</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCN3M</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Silicide block (Agilent/HP only)</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>
→ <u>SCN3ME</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>



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Technology code with link to layer map	Layers
<u>SCNE</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNA</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Pbase</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNPC</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly_cap</u> , <u>Poly</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCN3M</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Silicide block (Agilent/HP only)</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>
→ <u>SCN3ME</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>

## SCMOS Layout Rules - Well

Rule	Description	Lambda		
		SCMOS	SUBM	DEEP
1.1	Minimum width	10	12	12
1.2	Minimum spacing between wells at different potential	9 <sup>1</sup>	18 <sup>2</sup>	18
1.3	Minimum spacing between wells at same potential	6 <sup>3</sup>	6 <sup>4</sup>	6
1.4	Minimum spacing between wells of different type (if both are drawn)	0	0	0

Exceptions for AMIS C30 0.35 micron process:

<sup>1</sup> Use lambda=16 for rule 1.2 only when using SCN4M or SCN4ME

<sup>2</sup> Use lambda=21 for rule 1.2 only when using SCN4M\_SUBM or SCN4ME\_SUBM

<sup>3</sup> Use lambda=8 for rule 1.3 only when using SCN4M or SCN4ME

<sup>4</sup> Use lambda=11 for rule 1.3 only when using SCN4M\_SUBM or SCN4ME\_SUBM

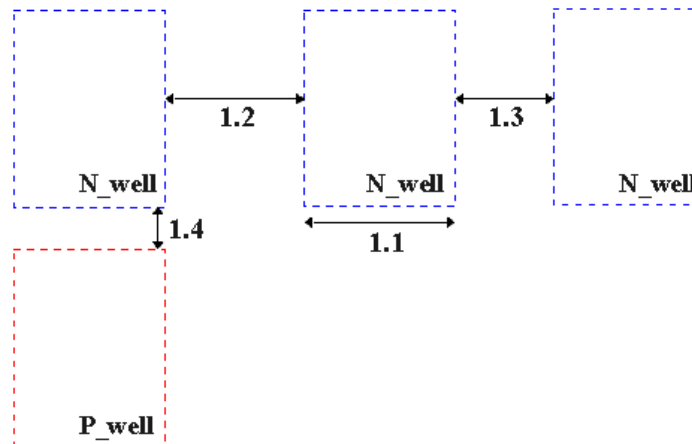


Table 5: Technology-code Map

Technology code with link to layer map	Layers
<u>SCNE</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNA</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Pbase</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNPC</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly_cap</u> , <u>Poly</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCN3M</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Silicide block (Agilent/HP only)</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>
→ <u>SCN3ME</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>

## SCMOS Layout Rules - Active

Rule	Description	Lambda		
		SCMOS	SUBM	DEEP
2.1	Minimum width	3 *	3 *	3
2.2	Minimum spacing	3	3	3
2.3	Source/drain active to well edge	5	6	6
2.4	Substrate/well contact active to well edge	3	3	3
2.5	Minimum spacing between non-abutting active of different implant. Abutting active ("split-active") is illustrated under <a href="#">Select Layout Rules</a> .	4	4	4

\* Note: For analog and critical digital designs, MOSIS recommends the following minimum MOS channel widths (active under poly) for AMIS designs. Narrower devices, down to design rule minimum, will be functional, but their electrical characteristics will not scale, and their performance is not predictable from MOSIS SPICE parameters.

Process	Design Technology	Design Lambda (micrometers)	Minimum Width (lambda)
AMI_ABN	SCNA, SCNE	0.80	5
AMI_C5F/N	SCN3M, SCN3ME	0.35	9
AMI_C5F/N	SCN3M_SUBM, SCN3ME_SUBM	0.30	10

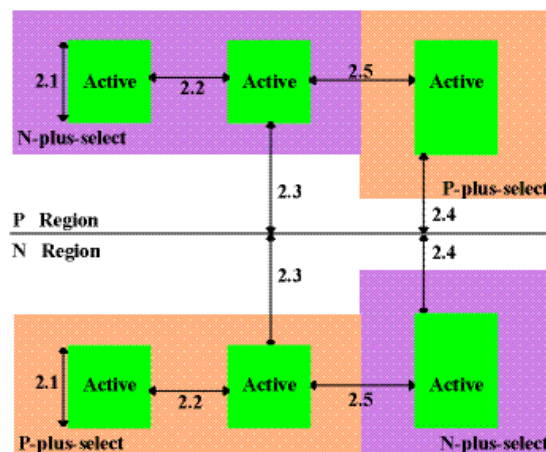


Table 5: Technology-code Map

Technology code with link to layer map	Layers
<u>SCNE</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNA</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Pbase</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNPC</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly_cap</u> , <u>Poly</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCN3M</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Silicide block (Agilent/HP only)</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>
→ <u>SCN3ME</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>

### SCMOS Layout Rules - Poly

Rule	Description	Lambda		
		SCMOS	SUBM	DEEP
3.1	Minimum width	2	2	2
3.2	Minimum spacing over field	2	3	3
3.2.a	Minimum spacing over active	2	3	4
3.3	Minimum gate extension of active	2	2	2.5
3.4	Minimum active extension of poly	3	3	4
3.5	Minimum field poly to active	1	1	1

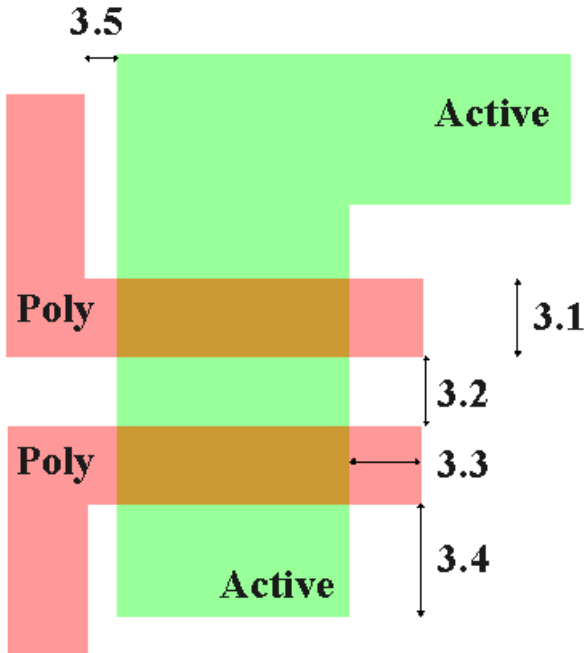


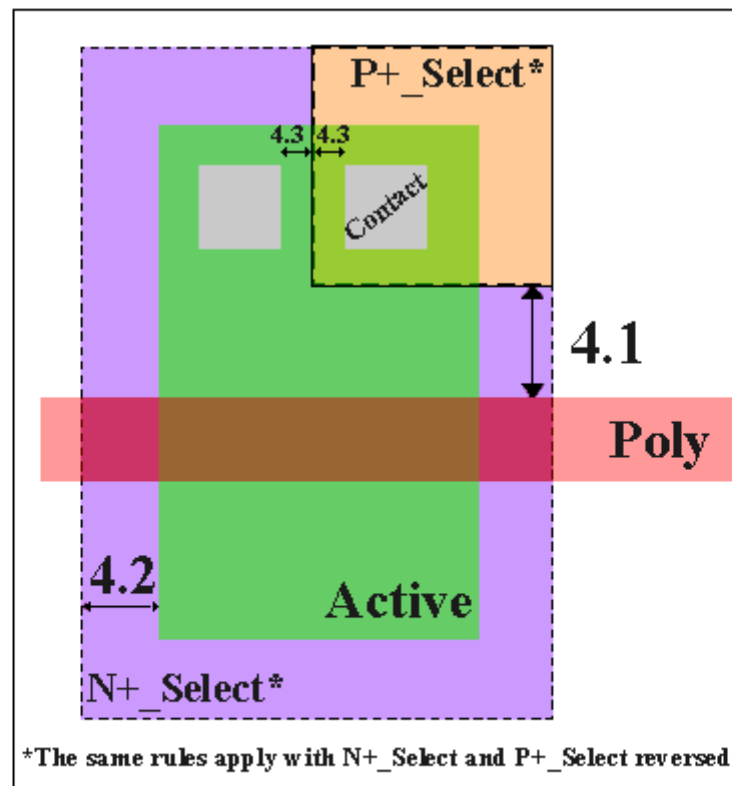


Table 5: Technology-code Map

Technology code with link to layer map	Layers
<u>SCNE</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNA</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Contact</u> , <u>Pbase</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCNPC</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly_cap</u> , <u>Poly</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Glass</u>
<u>SCN3M</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Silicide block (Agilent/HP only)</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>
→ <u>SCN3ME</u>	<u>N_well</u> , <u>Active</u> , <u>N_select</u> , <u>P_select</u> , <u>Poly</u> , <u>Poly2</u> , <u>Hi_Res_Implant</u> , <u>Contact</u> , <u>Metal1</u> , <u>Via</u> , <u>Metal2</u> , <u>Via2</u> , <u>Metal3</u> , <u>Glass</u>

## SCMOS Layout Rules - Select

Rule	Description	Lambda		
		SCMOS	SUBM	DEEP
4.1	Minimum select spacing to channel of transistor to ensure adequate source/drain width	3	3	3
4.2	Minimum select overlap of active	2	2	2
4.3	Minimum select overlap of contact	1	1	1.5
4.4	Minimum select width and spacing (Note: P-select and N-select may be coincident, but must <i>not</i> overlap) (not illustrated)	2	2	4





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End of Lecture 8